

mos integrated circuit $\mu PD78P064B$

8-BIT SINGLE-CHIP MICROCONTROLLER

DESCRIPTION

The μ PD78P064B is a product of μ PD78064B subseries in 78K/0 series, in which the on-chip mask ROM of the μ PD78064B is replaced by one-time PROM.

As program write by user is possible, the μ PD78P064B is best suited for evaluation, short-run and multiple-device production, and early rise upon system development.

Functions are described in detail in the following User's Manuals, which should be read when carrying out design work.

 μ PD78064B Subseries User's Manual: U10785E 78K/0 Series User's Manual Instruction: U12326E

FEATURES

- Pin compatible with mask ROM products (except the VPP pin)
- Internal PROM: 32K bytes

One-time programming possible (most suitable for small-scale production)

- Internal high-speed RAM: 1024 bytes
- LCD display RAM: 40 × 4 bits
- Operable in the same supply voltage as mask ROM products (VDD = 2.0 to 6.0 V)
- Corresponding to QTOP™ microcomputers
- Remarks 1. For the differences between PROM products and mask ROM products, refer to 1. DIFFERENCES BETWEEN μ PD78P064B AND MASK ROM PRODUCTS.
 - 2. QTOP Microcomputer is the general name for a total support as far as writing service, marking, screening, and verification after programming one-time PROM internal signal-chip microcontroller offered by NEC.

ORDERING INFORMATION

	Part Number	Package	On-Chip ROM	
	μPD78P064BGC-7EA	100-pin plastic QFP (fine pitch) (14 \times 14 mm)	One-time PROM	_
*	μ PD78P064BGC-8EU	100-pin plastic LQFP (fine pitch) (14 \times 14 mm)	One-time PROM	
	μ PD78P064BGF-3BA	100-pin plastic QFP (14 × 20 mm)	One-time PROM	

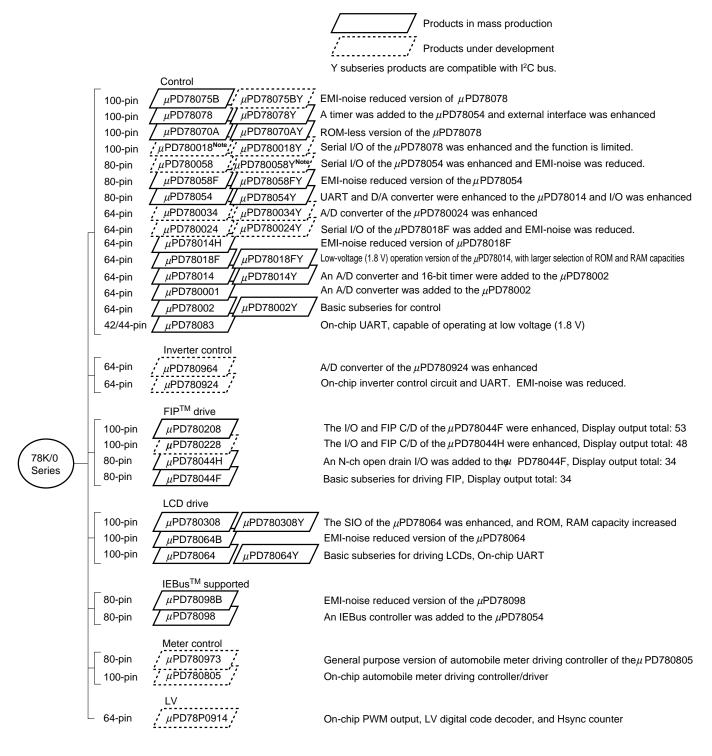
Caution The μ PD78P064BGC has two types of package. (Refer to 7. PACKAGE DRAWINGS). For the package suppliable to your device, consult NEC sales personnels.

The information in this document is subject to change without notice.



★ 78K/0 SERIES DEVELOPMENT

The following shows the products organized according to usage. The names in the parallelograms afe subseries names.



Note Under planning



The following lists the main functional differences between subseries products.

	Function	ROM		Tin	ner		8-bit	10-bit	8-bit	Serial Interface	I/O	VDD MIN.	External
Subseries	Name	Capacity	8-bit	16-bit	Watch	WDT	A/D	A/D	D/A	Senai interrace	1/0	Value	Expansion
Control	μPD78075B	32K-40K	4ch	1ch	1ch	1ch	8ch	-	2ch	3ch (UART: 1ch)	88	1.8 V	0
	μPD78078	48K-60K											
	μPD78070A	_									61	2.7 V	
	μPD780018	48K-60K							ı	2ch (time division 3-wire: 1ch)	88		
	μPD780058	24K-60K	2ch						2ch	3ch (time division UART: 1ch)	68	1.8 V	
	μPD78058F	48K-60K								3ch (UART: 1ch)	69	2.7 V	
	μPD78054	16K-60K										2.0 V	
	μPD780034	8K-32K					_	8ch	1	3ch (UART: 1ch,	51	1.8 V	
	μPD780024						8ch	_		time division 3-wire: 1ch)			
	μPD78014H									2ch	53	1.8 V	
	μPD78018F	8K-60K											
	μPD78014	8K-32K										2.7 V	
	μPD780001	8K		_	_					1ch	39		-
	μPD78002	8K-16K			1ch		_				53		0
	μPD78083				_		8ch			1ch (UART: 1ch)	33	1.8 V	_
Inverter	μPD780964	8K-32K	3ch	Note	_	1ch	-	8ch	-	2ch (UART: 2ch)	47	2.7 V	0
control	μPD780924						8ch	_					
FIP	μPD780208	32K-60K	2ch	1ch	1ch	1ch	8ch	-	-	2ch	74	2.7 V	-
drive	μPD780228	48K-60K	3ch	_	_					1ch	72	4.5 V	
	μPD78044H	32K-48K	2ch	1ch	1ch						68	2.7 V	
	μPD78044F	16K-40K								2ch			
LCD	μPD780308B	48K-60K	2ch	1ch	1ch	1ch	8ch	-	-	3ch (time division UART: 1ch)	57	2.0 V	_
drive	μPD78064	32K								2ch (UART: 1ch)			
	μPD78064	16K-32K											
IEBus	μPD78098B	40K-60K	2ch	1ch	1ch	1ch	8ch	1	2ch	3ch (UART: 1ch)	69	2.7 V	0
supported	μPD78098	32K-60K									L		
Meter	μPD780973	24K-32K	3ch	1ch	1ch	1ch	5ch	_	-	2ch (UART: 1ch)	56	4.5 V	_
control	μPD780805	40K-60K	2ch				8ch				39	2.7 V	
LV	μPD78P0914	32K	6ch	-	-	1ch	8ch	_	-	2ch	54	4.5 V	0

Note 10-bit timer: 1 channel



FUNCTION DESCRIPTION

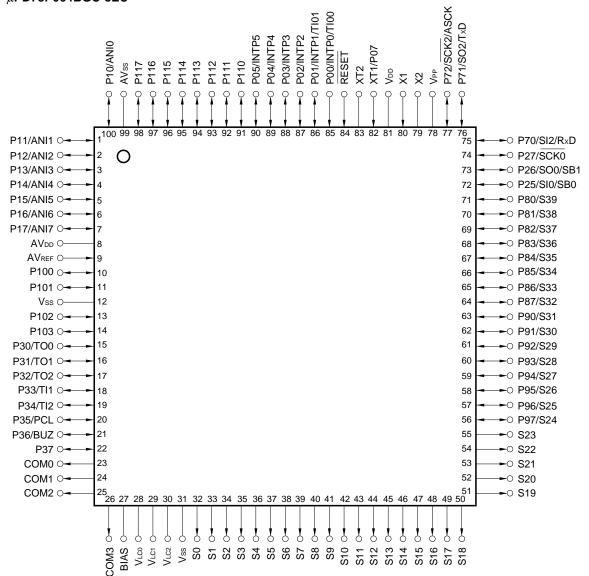
Item		Function			
Internal memory		PROM : 32 K bytes RAM High-speed RAM : 1024 bytes ^{Note} LCD display RAM : 40 × 4 bits			
General-purpo	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Instruction cycles	When main system clock is selected	0.4 μ s/0.8 μ s/1.6 μ s/3.2 μ s/6.4 μ s/12.8 μ s (when operating at 5.0 MHz)			
	When subsystem clock is selected	122 μ s (when operating at 32.768 kHz)			
Instruction set		 16-bit operation Multiplication/division (8 bits × 8 bits, 16 bits ÷ 8 bits) Bit manipulation (set, reset, test, boolean operation) BCD correction, etc. 			
	egment signal] al-function pin]	Total : 57 • CMOS input : 2 • CMOS input/output : 55			
A/D converter		8-bit resolution × 8 ch			
LCD controller/driver		 Segment signal output Common signal output Bias 40 max. 4 max. 1/2, 1/3, Bias switchable 			
Serial interface)	3-wire serial I/O/SBI/2-wire serial I/O mode selectable : 1 ch 3-wire serial I/O/UART mode selectable : 1 ch			
Timer		16-bit timer/event counter : 1 ch 8-bit timer/event counter : 2 ch Watch timer : 1 ch Watchdog timer : 1 ch			
Timer output		3 pins (14-bit PWM output enable 1 pin)			
Clock output		19.5 kHz, 39.1 kHz, 78.1 kHz, 156 kHz, 313 kHz, 625 kHz, 1.25 MHz, 2.5 MHz, 5.0 MHz (when operating at main system clock 5.0 MHz), 32.768 kHz (when operating at subsystem clock 32.768 kHz)			
Buzzer output		1.2 kHz, 2.4 kHz, 4.9 kHz, 9.8 kHz (when operating at main system clock 5.0 MHz)			
Vectored	Maskable	Internal : 12, External : 6			
interrupt sources	Non-maskable	Internal : 1			
Software		1			
Test input		Internal : 1, External : 1			
Supply voltage	1	V _{DD} = 2.0 to 6.0 V			
Package		 100-pin plastic (fine pitch) QFP (14 × 14 mm) 100-pin plastic LQFP (fine pitch) (14 × 14 mm) 100-pin plastic QFP (14 × 20 mm) 			

*



PIN CONFIGURATION (Top View)

- (1) Normal operating mode
 - 100-pin plastic QFP (fine pitch) (14 \times 14 mm) μ PD78P064BGC-7EA
- * 100-pin plastic LQFP (fine pitch) (14 \times 14 mm) μ PD78P064BGC-8EU

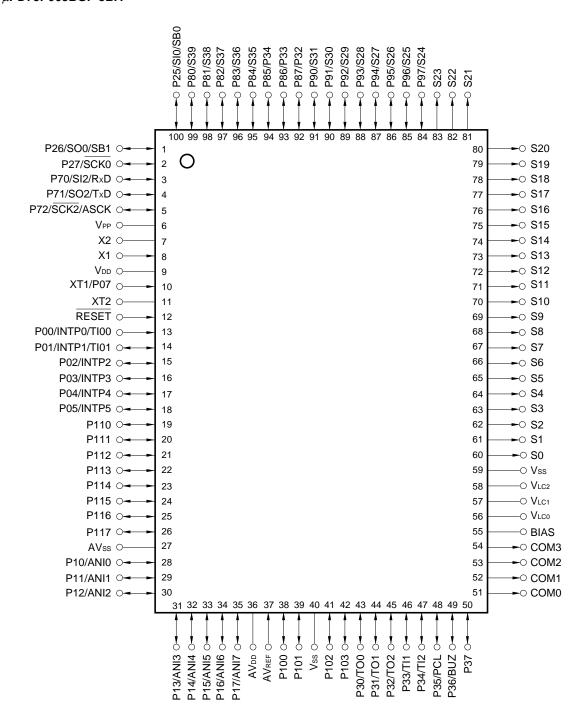


Cautions

- 1. Connect VPP pin directly to Vss.
- 2. AV_{DD} pin shares the port power supply with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AV_{DD} pin to a separate power supply, whose electrical potential is the same as that of V_{DD}.
- 3. AVss pin shares the port GND with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AVss pin to a separate ground line.



• 100-pin plastic QFP (14 × 20 mm) μ PD78P068BGF-3BA



- Cautions 1. Connect VPP pin directly to Vss.
 - AV_{DD} pin shares the port power supply with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AVDD pin to a separate power supply, whose electrical potential is the same as that of VDD.
 - 3. AVss pin shares the port GND with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AVss pin to a separate ground line.

Crystal (Main System Clock)

Crystal (Subsystem Clock)



P100-P103

P110-P117

Port 10

: Port 11

: Analog Input : Programmable Clock ANIO-ANI7 **PCL ASCK** Asynchronous Serial Clock RESET Reset AV_DD **Analog Power Supply** RxDReceive Data AV_{REF} : Analog Reference Voltage S0-S39 Segment Output **AVss** : Analog Ground SB0, SB1 Serial Bus **BIAS** LCD Power Supply Bias Control Serial Input SI0, SI2 BUZ **Buzzer Clock** SO0, SO2 Serial Output COM0-COM3 Common Output SCK0, SCK2 Serial Clock INTP0-INTP5 : Interrupt from Peripherals TI00, TI01 Timer Input P00-P05, P07 : Port 0 TI1,TI2 Timer Input P10-P17 : Port 1 TO0-TO2 **Timer Output** : Port 2 TxD Transmit Data P25-P27 P30-P37 : Port 3 V_{DD} **Power Supply** P70-P72 Port 7 V_{LC0} - V_{LC2} LCD Power Supply P80-P87 : Port 8 Vss Ground Port 9 V_{PP} **Programming Power Supply** P90-P97

X1, X2

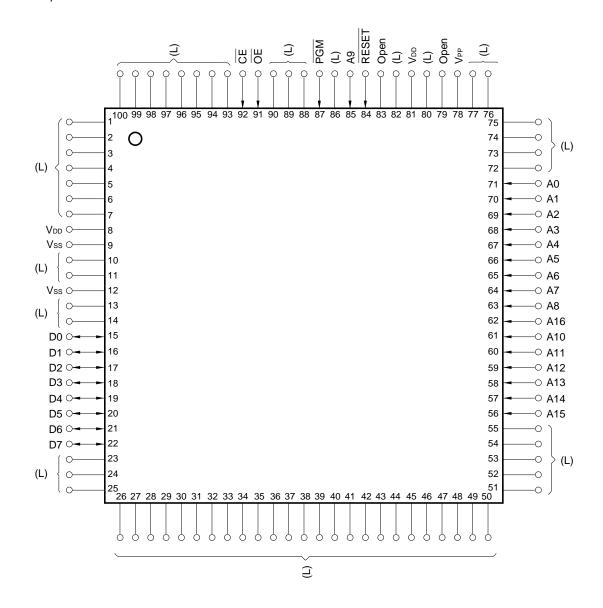
XT1, XT2



(2) PROM programming mode

- 100-pin plastic QFP (fine pitch) (14 \times 14 mm) μ PD78P064BGC-7EA
- 100-pin plastic LQFP (fine pitch) (14 × 14 mm)

★ μPD78P064BGC-8EU

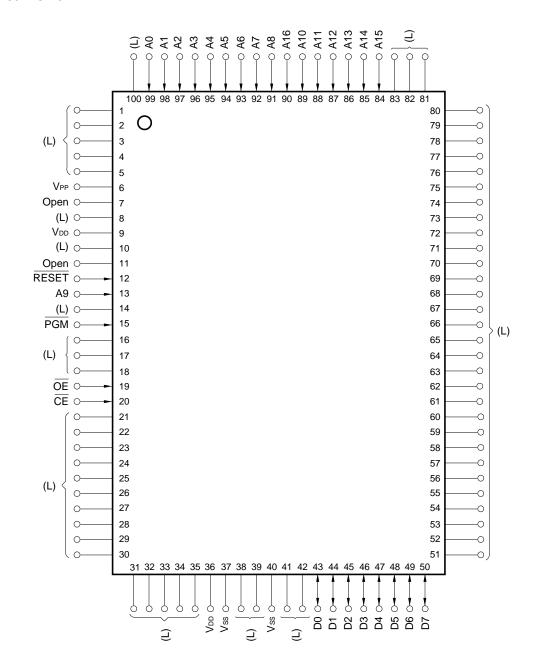


Cautions 1. (L) : Individually connect to Vss via a pull-down resistor.

Vss : Connect to GND.
 RESET : Set to low level.
 Open : No connection



• 100-pin plastic QFP (14 \times 20 mm) μ PD78P064BGF-3BA



Cautions 1. (L) : Individually connect to Vss via a pull-down resistor.

Vss : Connect to GND.
 RESET : Set to low level.
 Open : No connection

A0 to A16 : Address Bus RESET : Reset

CE : Chip Enable VDD : Power Supply

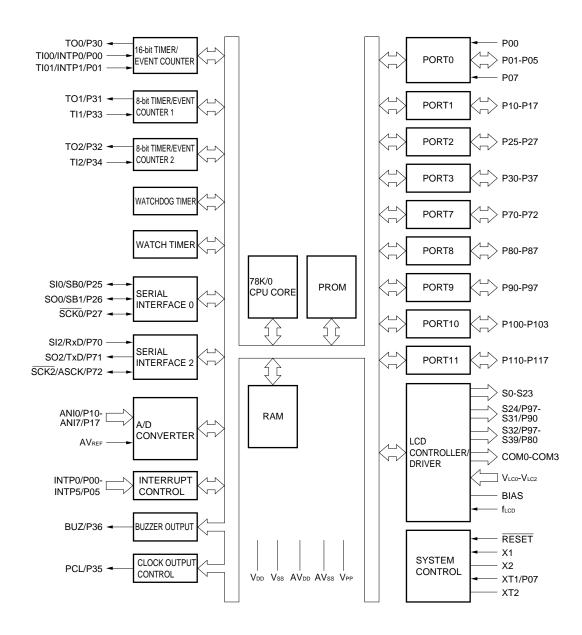
D0 to D7 : Data Bus VPP : Programming Power Supply

OE : Output Enable Vss : Ground

PGM : Program



BLOCK DIAGRAM





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1. DIFFERENCES BETWEEN μ PD78P064B AND MASK ROM PRODUCTS

The μ PD78P064B is a single-chip microcontroller with an on-chip one-time writable PROM.

It is possible to make all the functions exception PROM specification, and mask option of LCD drive power supply dividing resistor, to the same as those of mask ROM products by setting the memory size switching register (IMS).

Difference between the PROM product (μ PD78P064B) and mask ROM product (μ PD78064B) are shown is Table 1-1.

Table 1-1. Differences between μ PD78P064B and Mask ROM Products

Item	μPD78P064B	Mask ROM Products	
Internal ROM structure	One-time PROM	Mask ROM	
IC pin	No	Yes	
V _{PP} pin	Yes	No	
Mask option of LCD drive power supply dividing resistor	No	Yes	
Electrical characteristics	Refer to Data Sheet for each product		

★ Caution Noise resistance and noise radiation are different in PROM version and mask ROM versions. If using a mask ROM version instead of the PROM version for processes between prototype development and full production, be sure to fully evaluate the CS of the mask ROM version (not ES).

Remark The internal PROM becomes to 32K bytes and the internal high-speed RAM becomes 1024 bytes by the RESET input.



2. PIN FUNCTION TABLE

2.1 PINS IN NORMAL OPERATING MODE

(1) PORT PINS (1/2)

Pin Name	Input/Output		Function	After Reset	Dual-Function Pin
P00	Input	Port 0	Input only	Input	INTP0/TI00
P01	Input/output	7-bit input/output port	Input/output is specifiable	Input	INTP1/TI01
P02			bit-wise. When used as the input port,		INTP2
P03			an on-chip pull-up resistor can be used by software.		INTP3
P04					INTP4
P05					INTP5
P07 ^{Note 1}	Input		Input only	Input	XT1
P10 to P17	Input/output	Port 1 8-bit input/output port Input/output is specifiable bit-wise. When used as the input port, an on-chip pull-up resistor can be used by software. Note 2		Input	ANI0 to ANI7
P25	Input/output	Port 2	Input	SI0/SB0	
P26		3-bit input/output port Input/output is specifia			SO0/SB1
P27		can be used by softwa	ut port, an on-chip pull-up resistor re.		SCK0
P30	Input/output	Port 3		Input	TO0
P31		8-bit input/output port Input/output is specifia			TO1
P32		can be used by softwa	ut port, an on-chip pull-up resistor re.		TO2
P33					TI1
P34					TI2
P35					PCL
P36					BUZ
P37					
P70	Input/output	Port 7		Input	SI2/RxD
P71		3-bit input/output port Input/output is specifia			SO2/TxD
P72		can be used by softwa	ut port, an on-chip pull-up resistor re.		SCK2/ASCK

- Notes 1. When P07/XT1 pins are used as the input ports, set processor clock control register (PCC) bit 6 (FRC) to 1. (Do not use the on-chip feedback resistor of the subsystem clock oscillation circuit.)
 - 2. When P10/ANI0 to P17/ANI7 pins are used as the analog inputs for A/D converter, set port 1 to input mode. The on-chip pull-up resistor is automatically disabled.



(1) PORT PINS (2/2)

Pin Name	Input/Output	Function	After Reset	Dual-Function Pin
P80 to P87	Input/output	Port 8 8-bit input/output port Input/output is specifiable bit-wise. When used as the input port, an on-chip pull-up resistor can be used by software. Input/output port/segment signal output function specifiable in 2-bit units by LCD display control register (LCDC).	Input	S39 to S32
P90 to P97	Input/output	Port 9 8-bit input/output port. Input/output is specifiable bit-wise. When used as the input port, an on-chip pull-up resistor can be used by software. Input/output port/segment signal output function specifiable in 2-bit units by LCD display control register. (LCDC).	Input	S31 to S24
P100 to P103	Input/output	Port 10 4-bit input/output port Input/output is specifiable in bit-wise. When used as the input port, an on-chip pull-up resistor can be used by software. It is possible to directly drive LED.	Input	
P110 to P117	Input/output	Port 11 8-bit input/output port Input/output is specifiable in bit-wise. When used as the input port, an on-chip pull-up resistor can be used by software. Falling edge detection possible.	Input	

Caution Do not perform the following operation on the pins shared with port pins during A/D conversion operation; otherwise, the specifications of the total error during A/D conversion cannot be satisfied (except the pins shared with LCD segment output pins).

- (1) Rewriting the output latch of an output pin used as a port pin
- (2) Changing the output level of an output pin even when it is not used as a port pin



(2) PINS OTHER THAN PORT PINS (1/2)

Pin Name	Input/Output	Function	After Reset	Dual-Function Pin
INTP0	Input	External interrupt request input with specifiable Valid	Input	P00/TI00
INTP1		edges (rising edge, falling edge, and both rising and falling edges).		P01/TI01
INTP2				P02
INTP3				P03
INTP4				P04
INTP5				P05
SI0	Input	Serial data input of the serial interface	Input	P25/SB0
SI2				P70/R×D
SO0	Output	Serial data output of the serial interface	Input	P26/SBI
SO2				P71/TxD
SB0	Input/output	Serial data input/output of the serial interface	Input	P25/SI0
SB1				P26/SO0
SCK0	Input/output	Serial clock input/output of the serial interface	Input	P27
SCK2				P72/ASCK
RxD	Input	Serial data input for asynchronouse serial interface	Input	P70/SI2
TxD	Outpu	Serial data output for asynchronous serial interface	Input	P71/SO2
	Input	Serial clock input for asynchronous serial interface	Input	
ASCK	•		Input	P72/SCK2
T100	Input	External count clock input to the 16-bit timer (TM0).	Input	P00/INTP0
TI01		Capture trigger signal input to the capture register (CR00).		P01/INTP1
TI1		External count clock input to the 8-bit timer (TM1).		P33
TI2		External count clock input to the 8-bit timer (TM2).		P34
TO0	Output	16-bit timer (TM0) output (dual-function as 14-bit PWM output)	Input	P30
TO1		8-bit timer (TM1) output		P31
TO2		8-bit timer (TM2) output		P32
PCL	Output	Clock output (for trimming main system clock and subsystem clock)	Input	P35
BUZ	Output	Buzzer output	Input	P36
S0 to S23	Output	LCD controller/driver segment signal output	Output	
S24 to S31			Input	P97-P90
S32 to S39				P87-P80
COM0 to COM3	Output	LCD controller/driver common signal output	Output	
VLC0 to VLC2		LCD drive voltage		
BIAS		LCD drive power supply		



(2) PINS OTHER THAN PORT PINS (2/2)

Pin Name	Input/Output	Function	After Reset	Dual-Function Pin
ANI0 to ANI7	Input	Analog input of A/D converter	Input	P10 to P17
AVREF	Input	Reference voltage input of A/D converter		
AVDD		Analog power supply of A/D converter (shared by power supply of port)		
AVss		Ground potential of A/D converter (shared by ground potential of port)		
RESET	Input	System reset input		
X1	Input	Main system clock oscillation crystal connection		
X2				
XT1	Input	Subsystem clock oscillation crystal connection	Input	P07
XT2				
V _{DD}		Positive power supply (except port)		
V _{PP}		High-voltage applied during program write/verification Connected directly to Vss in normal operating mode		
Vss		Ground potential (except port)		

- Cautions 1. AVDD pin shares the port power supply with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AV_DD pin to a separate power supply, whose electrical potential is the same as that of $\ensuremath{\text{V}_{\text{DD}}}$.
 - 2. AVss pin shares the port GND with that of the A/D converter. When using in applications where noise from inside the microcomputer has to be reduced, connect the AVss pin to a separate ground line.

2.2 PINS IN PROM PROGRAMMING MODE

Pin Name	Input/Output	Function	
RESET	Input	PROM programming mode setting When +5 V or +12.5 V is applied to the VPP pin and a low level signal is applied to the RESET pin, this chip is set in the PROM programming mode.	
Vpp	Input	PROM programming mode setting and high-voltage applied during program write/verification	
A0 to A16	Input	Address bus	
D0 to D7	Input/output	Data bus	
CE	Input	PROM enable input/program pulse input	
ŌĒ	Input	Read strobe input to PROM	
PGM	Input	Program/program inhibit input in PROM programing mode.	
V _{DD}		Positive power supply	
Vss		Ground potential	



2.3 PIN INPUT/OUTPUT CIRCUITS AND RECOMMENDED CONNECTION OF UNUSED PINS

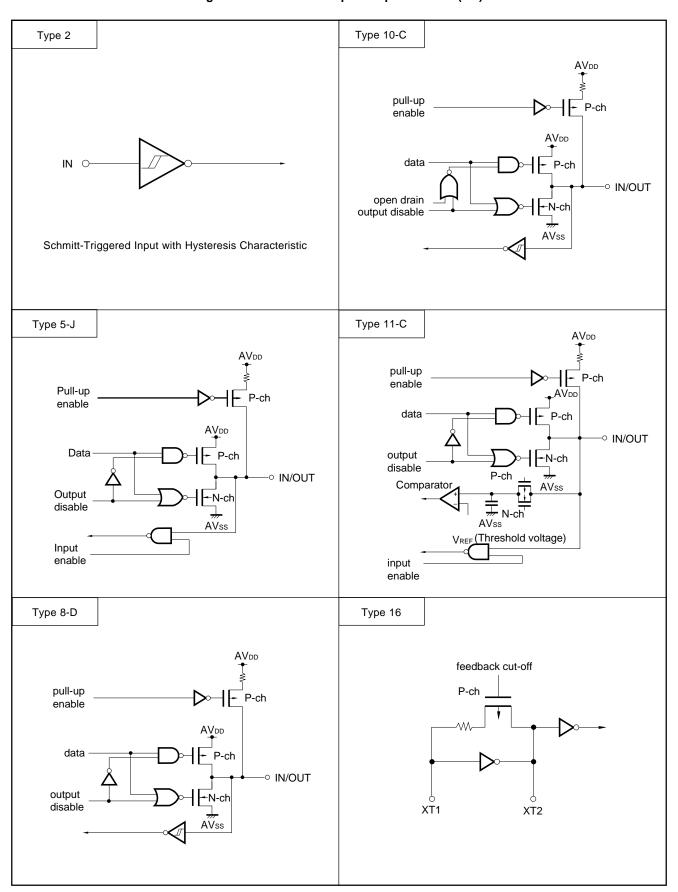
Types of input/output circuits of the pins and recommended connection of unused pins are shown in Table 2-1. For the configuration of each type of input/output circuit, refer to Figure 2-1.

Table 2-1. Type of Input/Output Circuit of Each Pin

Pin Name	Input/Output Circuit Type	I/O	Recommended Connection When not Used
P00/INTP0/TI00	2	Input	Connect to Vss.
P01/INTP1/TI01	8-D	I/O	Individually connect to Vss via a resistor
P02/INTP2			
P03/INTP3			
P04/INTP4			
P05/INTP5			
P07/XT1	16	Input	Connect to VDD.
P10/ANI0 to P17/ANI7	11-C	I/O	Individually connect to VDD or VSS via a resistor
P25/SI0/SB0	10-C		
P26/SO0/SB1	1		
P27/SCK0	1		
P30/TO0	5-J		
P31/TO1]		
P32/TO2	1		
P33/TI1	8-D		
P34/TI2	1		
P35/PCL	5-J		
P36/BUZ	1		
P37	1		
P70/SI2/RxD	8-D		
P71/SO2/TxD	5-J		
P72/SCK2/ASCK	8-D		
P80/S39 to P87/S32	17-E		
P90/S31 to P97/S24	1		
P100 to P103	5-J		
P110 to P117	8-D		Individually connect to VDD via resistor
S0 to S23	17-D	Output	Leave open
COM0 to COM3	18-B		
VLC0 to VLC2			
BIAS	1		
RESET	2	Input	
XT2	16		Leave open
AVREF			Connect to Vss
AV _{DD}			Connect to separate power supply whose electrical potential is the same as that of VDD.
AVss			Connect to separate ground line whose electrical potential is the same as that of Vss.
V _{PP}]		Connect directly to Vss



Figure 2-1. List of Pin Input/Output Circuits (1/2)





Type 17-D Type 18-B V_{LC0} V_{LC0} V_{LC1} V_{LC1} N-ch P-ch P-ch SEG ⊸ out data ⊸ out P-ch COM data N-ch L N-ch V_{LC2} V_{LC2} Vss Type 17-E AVDD pull-up enable data -O IN/OUT output disable N-ch AVss input enable V_{LC0} $V_{LC1} \\$ N-ch P-ch SEG data N-ch V_{LC2}

Figure 2-1. List of Pin Input/Output Circuits (2/2)



3. MEMORY SIZE SWITCHING REGISTER (IMS)

This is a register to disable use of part of internal memories by software. By setting this memory size switching register (IMS), it is possible to get the same memory mapping as that of mask ROM product having different internal memories (ROM, RAM).

The IMS is set up by the 8-bit memory manipulating instruction.

C8H will result by the RESET input.

Figure 3-1. Memory Size Switching Register Format

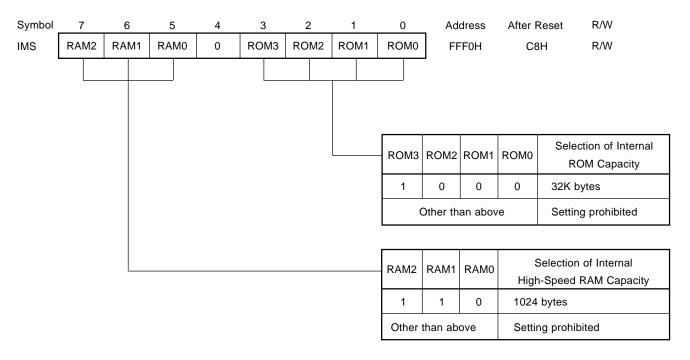


Table 3-1 shows the set values of IMS which makes the memory map the same as that of the various mask ROM products.

Table 3-1. Memory Size Switching Register Setting Values

Target Mask ROM Product	IMS Setting Value
μPD78064B	С8Н



4. PROM PROGRAMMING

The μ PD78P064B has an on-chip 32K-byte PROM as a program memory. For programming, set the PROM programming mode by the V_{PP} and $\overline{\text{RESET}}$ pins. For processing unused pins, refer to **Pin Configuration (2) PROM programming mode**.

Caution When writing in a program, use locations 0000H-7FFFH. (Specify the last address as 7FFFH). You cannot write in using a PROM programmer that cannot specify the addresses to write.

4.1 OPERATING MODES

When +5 V or +12.5 V is applied to the VPP pin and a low level signal is applied to the $\overline{\text{RESET}}$ pin, the PROM programming mode is set. This mode will become the operating mode as shown in Table 4-1 when the $\overline{\text{CE}}$, $\overline{\text{OE}}$ and $\overline{\text{PGM}}$ pins are set as shown.

Further, when the read mode is set, it is possible to read the contents of the PROM.

Table 4-1. Operating Modes of PROM Programming

Pin Operating Mode	RESET	Vpp	Vod	CE	ŌĒ	PGM	D0 to D7
Page data latch	L	+12.5 V	+6.5 V	Н	L	Н	Data input
Page write				Н	Н	L	High-impedance
Byte write				L	Н	L	Data input
Program verify				L	L	Н	Data output
Program inhibit				×	Н	Н	High-impedance
				×	L	L	
Read		+5 V	+5 V	L	L	Н	Data output
Output disable				L	Н	×	High-impedance
Standby				Н	×	×	High-impedance

 \times : L or H



(1) Read mode

Read mode is set if $\overline{CE} = L$, $\overline{OE} = L$ is set.

(2) Output disable mode

Data output becomes high-impedance, and is in the output disable mode, of $\overline{OE} = H$ is set.

Therefore, it allows data to be read from any device by controlling the $\overline{\text{OE}}$ pin, if multiple $\mu\text{PD78P064Bs}$ are connected to the data bus.

(3) Standby mode

Standby mode is set if $\overline{CE} = H$ is set.

In this mode, data outputs become high-impedance irrespective of the $\overline{\text{OE}}$ status.

(4) Page data latch mode

Page data latch mode is set if $\overline{CE} = H$, $\overline{PGM} = H$, $\overline{OE} = L$ are set at the beginning of page write mode. In this mode, 1 page 4-byte data is latched in an internal address/data latch circuit.

(5) Page write mode

After 1 page 4 bytes of addresses and data are latched in the page data latch mode, a page write is executed by applying a 0.1 ms program pulse (active low) to the \overline{PGM} pin with $\overline{CE} = H$, $\overline{OE} = H$. Then, program verification can be performed, if $\overline{CE} = L$, $\overline{OE} = L$ are set.

If programming is not performed by a one-time program pulse, X ($X \le 10$) write and verification operations should be executed repeatedly.

(6) Byte write mode

Byte write is executed when a 0.1 ms program pulse (active low) is applied to the \overline{PGM} pin with $\overline{CE} = L$, $\overline{OE} = H$. Then, program verification can be performed if $\overline{OE} = L$ is set.

If programming is not performed by a one-time program pulse, X ($X \le 10$) write and verification operations should be executed repeatedly.

(7) Program verify mode

Program verify mode is set if $\overline{CE} = L$, $\overline{PGM} = H$, $\overline{OE} = L$ are set. In this mode, check if a write operation is performed correctly, after the write.

(8) Program inhibit mode

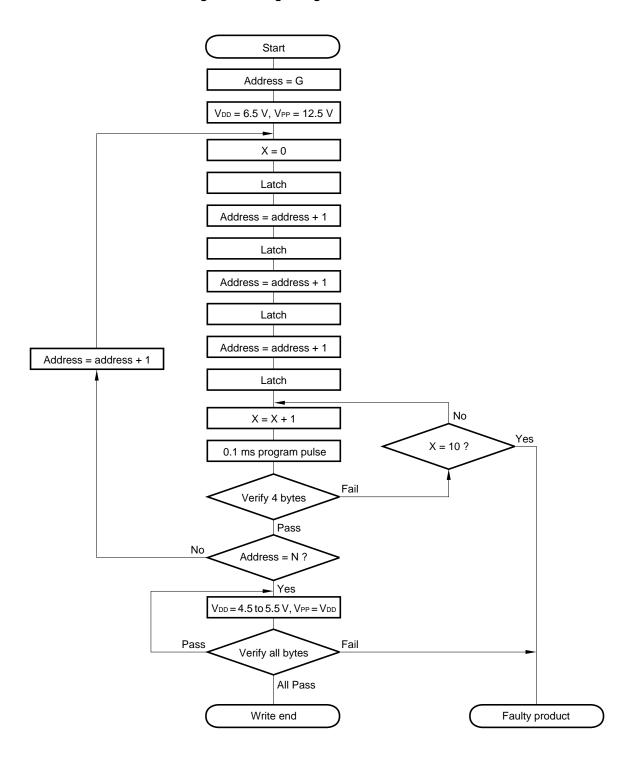
Program inhibit mode is used when the $\overline{\text{OE}}$ pin, VPP pin and D0 to D7 pins of multiple μ PD78P064Bs are connected in parallel and a write is performed to one of those devices.

When a write operation is performed, the page write mode or byte write mode described above is used. At this time, a write is not performed to a device which has the \overline{PGM} pin driven high.



4.2 PROM WRITE PROCEDURE

Figure 4-1. Page Program Mode Flow Chart

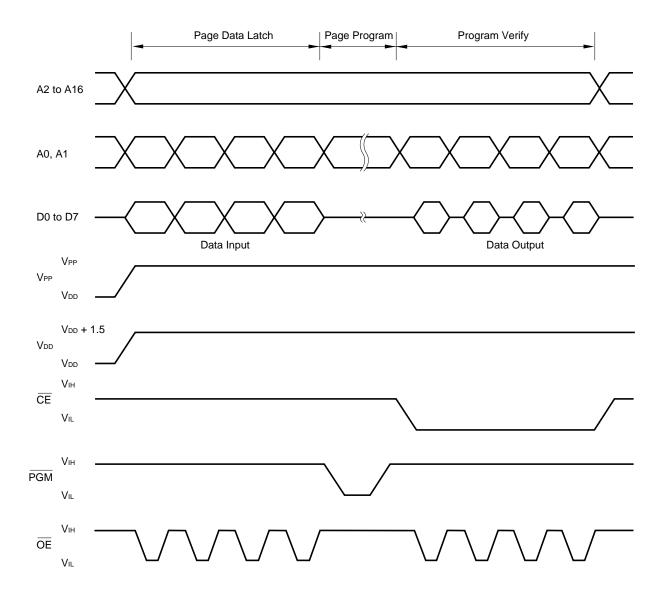


G = Start address

N = Program last address



Figure 4-2. Page Program Mode Timing



Start Address = G $V_{DD} = 6.5 \text{ V}, V_{PP} = 12.5 \text{ V}$ X = 0X = X + 1No Yes X = 10 ? 0.1 ms Program pulse Address = address + 1 Fail Verify Pass No Address = N? Yes $V_{DD} = 4.5 \text{ to } 5.5 \text{ V}, V_{PP} = V_{DD}$ Pass Fail Verify all bytes All Pass Write end Faulty product

Figure 4-3. Byte Program Mode Flow Chart

G = Start address

N = Program last address



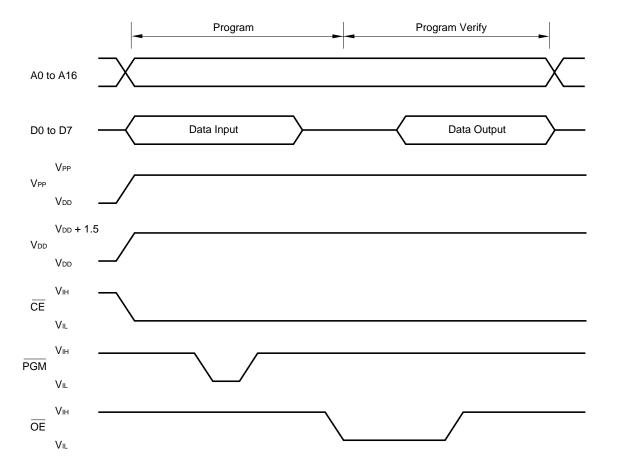


Figure 4-4. Byte Program Mode Timing

- Cautions 1. VDD should be applied before VPP and cut after VPP.
 - 2. VPP must not exceed +13.5 V including overshoot.
 - 3. Reliability may be adversely affected of removal/reinsertion is performed while +12.5 V is being applied to VPP.



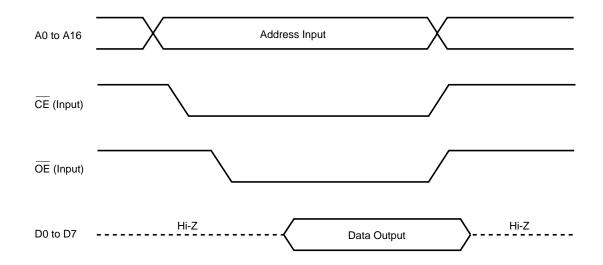
4.3 PROM READ PROCEDURE

The contents of PROM are readable to the external data bus (D0 to D7) according to the read procedure shown below.

- (1) Fix the RESET pin at low level, supply +5 V to the VPP pin, and process all other unused pins as shown in **Pin** Configuration (2) PROM programming mode.
- (2) Supply +5 V to the VDD and VPP pins.
- (3) Input address of read data into the A0 to A16 pins.
- (4) Read mode
- (5) Output data to D0 to D7 pins.

The timings of the above steps (2) to (5) are shown in Figure 4-5.

Figure 4-5. PROM Read Timings





5. ONE-TIME PROM PRODUCTS SCREENING

The one-time PROM product (μ PD78P064BGC-7EA, μ PD78P064BGC-8EU, μ PD78P064BGF- 3BA) can not be tested completely by NEC before it is shipped, because of its structure. It is recommended to perform screening to verify PROM after writing necessary data and performing high-temperature storage under the condition below.

Storage Temperature	Storage Time
125 °C	24 hours

At present, a fee is charged by NEC for one-time PROM after-programming writing, marking, screening, and verify service for the QTOP Microcomputer. For details, contact your sales representative.



6. ELECTRICAL SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Parameter	Symbol	Test 0	Conditions		Rating	Unit
	V _{DD}				-0.3 to +7.0	V
	V _{PP}				-0.3 to +13.5	V
Supply voltage	AV _{DD}				-0.3 to V _{DD} +0.3	V
	AVREF				-0.3 to V _{DD} +0.3	V
	AVss				-0.3 to +0.3	V
Input voltage	Vı	P00-P05, P07, P10-P1 P30-P37, P70-P72, P80 P100-P103, P110-P117	0-P87, P90		-0.3 to V _{DD} +0.3	V
	V ₁₂	A9 (PROM programmir	ng mode)		-0.3 to +13.5	V
Output voltage	Vo	_			-0.3 to V _{DD} +0.3	V
Analog input voltage	Van	P10-P17 Analog input pin		AVss -0.3 to AVREF +0.3	V	
		1 pin	'	-10	mA	
Output current, high	Іон	Total for P01-P05, P10 P70-P72, P80-P87, P90 P110-P117		-15	mA	
		d min		Peak value	30	mA
		1 pin		R.m.s. value	15	mA
Output current, low	loL ^{Note}	Total for P01-P05, P10 P25-P27, P30-P37, P7	-	Peak value	100	mA
				R.m.s. value	70	mA
Operating ambient temperature	TA				-40 to +85	°C
Storage temperature	Tstg				-65 to +150	°C

Note The r.m.s. value should be calculated as follows: [R.m.s. value] = [Peak value] $\times \sqrt{\text{Duty}}$

Caution The product quality may be damaged even if a value of only one of the above parameters exceeds the absolute maximum rating or any value exceeds the absolute maximum rating for an instant. That is, the absolute maximum rating is a rating value which may cause a product to be damaged physically. The absolute maximum rating values must therefore be observed in using the product.

Remark Unless specified otherwise, the characteristics of dual-function pins are the same as the those of port pins.

CAPACITANCE (TA= 25 °C, VDD = Vss = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	f = 1 MHz unmeasured			15	pF
Output capacitance	Соит	pins returned to 0 V.			15	pF
I/O capacitance	Сю	pins returned to 0 v.			15	pF



MAIN SYSTEM CLOCK OSCILLATION CIRCUIT CHARACTERISTICS (TA = -40 to +85 °C, VDD = 2.0 to 6.0 V)

Resonator	Recommended circuit	Parameter	Test conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator	c2 C1 7/77	Oscillator frequency (fx)Note 1	V _{DD} = Oscillator voltage range	1		5	MHz
		Oscillation stabilization time ^{Note 2}	After V _{DD} reaches oscillator voltage range MIN.			4	ms
Crystal resonator	YPP AZ AT	Oscillator frequency (fx)Note 1		1		5	MHz
	C2 + C1+	Oscillation	V _{DD} = 4.5 to 6.0 V			10	mo
	777	stabilization time ^{Note 2}				30	ms
External clock	X2 X1	X1 input frequency (fx)Note 1		1.0		5.0	MHz
μPD7	□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□	X1 input high/low level width (txH, txL)		85		500	ns

- Notes 1. Indicates only oscillation circuit characteristics. Refer to "AC Characteristics" for instruction execution time.
 - 2. Time required to stabilize oscillation after reset or STOP mode release.

Cautions 1. When using the main system clock oscillator, wiring in the area enclosed with the broken line should be carried out as follows to avoid an adverse effect from wiring capacitance.

- · Wiring should be as short as possible.
- · Wiring should not cross other signal lines.
- · Wiring should not be placed close to a varying high current.
- The potential of the oscillator capacitor ground should be the same as Vss.
- Do not ground it to the ground pattern in which a high current flows.
- Do not fetch a signal from the oscillator.
- 2. If the main system clock oscillation circuit is operated by the subsystem clock when the main system clock is stopped, reswitching to the main system clock should be performed after the stable oscillation time has been obtained by the program.



SUBSYSTEM CLOCK OSCILLATOR CHARACTERISTICS (TA = -40 to +85°C, VDD = 2.0 to 6.0 V)

Resonator	Recommended Circuit	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator	V _{PP} XT1 XT2	Oscillator frequency (fxT)Note 1		32	32.768	35	kHz
	C3 = C4 =	Oscillation stabilization	V _{DD} = 4.5 to 6.0 V		1.2	2	S
	\ ' 7/7	time ^{Note 2}				10	
External clock	XT1 XT2	XT1 input frequency (fxr)Note 1		32		100	kHz
	A	XT1 input high-/low-level width (tхтн/tхть)		5		15	μs

- Notes 1. Indicates only oscillation circuit characteristics. Refer to "AC Characteristics" for instruction execution time.
 - 2. Time required to stabilize oscillation after VDD has reached the minimum oscillation voltage range.
- Cautions 1. When using the subsystem clock oscillator, wiring in the area enclosed with the broken line should be carried out as follows to avoid an adverse effect from wiring capacitance.
 - · Wiring should be as short as possible.
 - · Wiring should not cross other signal lines.
 - Wiring should not be placed close to a varying high current.
 - The potential of the oscillator capacitor ground should be the same as Vss.
 - . Do not ground it to the ground pattern in which a high current flows.
 - Do not fetch a signal from the oscillator.
 - The subsystem clock oscillation circuit is designed as a low amplification circuit to provide low consumption current, causing misoperation to noise more frequently than the main system clock oscillation circuit. Special care should therefore be taken to wiring method when the subsystem clock is used.



RECOMMENDED OSCILLATION CIRCUIT CONSTANT

MAIN SYSTEM CLOCK: CERAMIC RESONATOR (T_A = -40 to +85 °C)

Manufaturer	Product Name	Frequency	Recommended Circuit Constant			llator Range	Remarks
		(MHZ)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)	
Murata Mfg.	CSA5.00MG	5.00	30	30	2.7	6.0	
Co., Ltd.	CST5.00MGW	5.00	Built-in	Built-in	2.7	6.0	
Matsushita	EF0GC5004A4	5.00	Built-in	Built-in	2.7	6.0	Lead type
Electronics	EF0EC5004A4	5.00	Built-in	Built-in	2.7	6.0	Round lead type
Components	EF0EN5004A4	5.00	33	33	2.7	6.0	Lead type
Co., Ltd.	EF0S5004B4	5.00	Built-in	Built-in	2.7	6.0	Chip type
	KBR-5.0MSA	5.00	33	33	2.7	6.0	Lead type
Kyocera	PBRC5.00A	5.00	33	33	2.7	6.0	Chip type
Corporation	KBR-5.0MKS	5.00	Built-in	Built-in	2.7	6.0	Lead type
	KBR-5.0MWS	5.00	Built-in	Built-in	2.7	6.0	Chip type

Caution

The oscillation circuit constants and oscillation voltage range indicate conditions for stable oscillation but do not guarantee accuracy of the oscillation frequency. If the application circuit requires accuracy of the oscillation frequency, it is necessary to set the oscillation frequency in the application circuit. For this, it is necessary to directly contact the manufacturer of the resonator being used.



DC CHARACTERISTICS ($T_A = -40 \text{ to } +85^{\circ}\text{C}$, $V_{DD} = 2.0 \text{ to } 6.0 \text{ V}$)

Parameter	Symbol	Test Cor	nditions	MIN.	TYP.	MAX.	Unit
	V _{IH1}	P10-P17, P30-P32, P35-P37, P80-P87,	V _{DD} = 2.7 to 6.0 V	0.7 Vdd		V _{DD}	V
		P90-P97, P100-P103		0.8 V _{DD}		V _{DD}	V
		P00-P05, P25-P27,	V _{DD} = 2.7 to 6.0 V	0.8 V _{DD}		V _{DD}	V
	V _{IH2}	P33, P34, P70-P72, P110-P117, RESET		0.85 V _{DD}		V _{DD}	V
Input voltage, high			V _{DD} = 2.7 to 6.0 V	V _{DD} -0.5		V _{DD}	V
9	Vінз	X1, X2		V _{DD} -0.2		V _{DD}	V
			4.5 ≤ V _{DD} ≤ 6.0 V	0.8 V _{DD}		V _{DD}	V
	V _{IH4}	XT1/P07, XT2	2.7 ≤ V _{DD} < 4.5 V	0.9 V _{DD}		V _{DD}	V
			$2.0 \le V_{DD} < 2.7 \ V^{\text{Note}}$	0.9 V _{DD}		V _{DD}	V
		P10-P17, P30-P32,	V _{DD} = 2.7 to 6.0 V	0		0.3 V _{DD}	V
	VIL1	P35-P37, P80-P87, P90-P97, P100-P103		0		0.2 V _{DD}	V
	,,	P00-P05, P25-P27,	V _{DD} = 2.7 to 6.0 V	0		0.2 V _{DD}	V
Input voltage,	V _{IL2}	P33, P34, P70-P72, P110-P117, RESET		0		0.15 V _{DD}	V
low	,,		V _{DD} = 2.7 to 6.0 V	0		0.4	V
	VIL3	X1, X2		0		0.2	V
			4.5 ≤ V _{DD} ≤ 6.0 V	0		0.2 V _{DD}	V
	VIL4	XT1/P07, XT2	2.7 ≤ V _{DD} < 4.5 V	0		0.1 V _{DD}	V
			$2.0 \le V_{DD} < 2.7 V^{\text{Note}}$	0		0.1 V _{DD}	V
Output voltage,	.,	V _{DD} = 4.5 to 6.0 V	1 mA	V _{DD} -1.0		V _{DD}	V
high	Vон	Ioн = -100 μA		V _{DD} -0.5		V _{DD}	V
		P100-P103	V _{DD} = 4.5 to 6.0 V, I _{OL} = 15 mA		0.4	2.0	V
Output voltage,	Vol1	P01-P05, P10-P17, P25-P27, P30-P37, P70-P72, P80-P87, P90-P97, P110-P117	V _{DD} = 4.5 to 6.0 V, I _{OL} = 1.6 mA			0.4	V
	Vol2	SB0, SB1, SCK0	V _{DD} = 4.5 to 6.0 V,			0.2 V _{DD}	V
	Vol3	IoL = 400 μA	•			0.5	V

Note When used as P07, the inverse phase of P07 should be input to XT2 using an inverter.

Remark Unless specified otherwise, the characteristics of dual-function pins are the same as the those of port pins.



DC CHARACTERISTICS (T_A = -40 to +85 °C, V_{DD} = 2.0 to 6.0 V)

Parameter	Symbol	Test C	onditi	ions	MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішні	VIN = VDD	P30 P90	-P05, P10-P17, P25-P27, -P37, P70-P72, P80-P87, -P97, P100-P103, 0-P117			3	μΑ
	I _{LIH2}		X1,	X2, XT1/P07, XT2			20	μΑ
Input leakage current, low	ILIL1	V _{IN} = 0 V	P30- P90-	-P05, P10-P17, P25-P27, -P37, P70-P72, P80-P87, -P97, P100-P103, 0-P117			-3	μΑ
	Ілн2	VIN = 0 V	X1,	X2, XT1/P07, XT2			-20	μΑ
Output leakage current, high	Ісон	Vout = Vdd	r = V _{DD}				3	μΑ
Output leakage current, low	ILOL	Vout = 0 V	Vout = 0 V				-3	μΑ
Software			V _{IN} = 0 V, P01-P05, P10-P17, P25-P27, P30-P37, P70-P72,		15	40	90	kΩ
pull-up resistor	K	P80-P87, P90-P97, P100-P103, P110-P117		2.7 V ≤ V _{DD} < 4.5 V	20		500	kΩ
		5.00 MHz, Crystal oscillation	on	$V_{DD} = 5.0 \text{ V} \pm 10 \%^{\text{Note 5}}$		5.0	15.0	mA
		$(fxx = 2.5 \text{ MHz})^{\text{Note 2}}$		$V_{DD} = 3.0 \text{ V} \pm 10 \%^{\text{Note 6}}$		0.7	2.1	mA
	I _{DD1}	operating mode		$V_{DD} = 2.2 \text{ V} \pm 10 \%^{\text{Note 6}}$		0.4	1.2	mA
		5.00 MHz, Crystal oscillation (fx: = 5.0 MHz) ^{Note 3} operating mode		$V_{DD} = 5.0 \text{ V} \pm 10 \%^{\text{Note 5}}$		9.0	27.0	mA
		= 5.0 MHz) ^{Note 3} operating r	moae			1.0	3.0	mA
		5.00 MHz, Crystal oscillation		$V_{DD} = 5.0 \text{ V} \pm 10 \%$		1.4	4.2	mA
		$(fxx = 2.5 \text{ MHz})^{\text{Note 2}}$		$V_{DD} = 3.0 \text{ V} \pm 10 \%$		500	1500	μΑ
	I _{DD2}	HALT mode	"	V _{DD} = 2.2 V ± 10 %		280	840	μΑ
		5.00 MHz, Crystal oscillation = 5.0 MHz) ^{Note 3} HALT mod	n (txx le	$V_{DD} = 5.0 \text{ V} \pm 10 \%$		1.6	4.8	mA
0		= 3.0 WHZ) TIALT HOU		V _{DD} = 3.0 V ± 10 %		650	1950	μΑ
Supply current ^{Note 1}	I _{DD3}	32.768 kHz, Crystal oscillat	tion	$V_{DD} = 5.0 \text{ V} \pm 10 \%$		135	270	μΑ
current	1003	operating modeNote 4		$V_{DD} = 3.0 \text{ V} \pm 10 \%$		95	190	μΑ
				$V_{DD} = 2.2 \text{ V} \pm 10 \%$		70	140	μΑ
	I _{DD4}	32.768 kHz, Crystal oscillat	tion	$V_{DD} = 5.0 \text{ V} \pm 10 \%$		25	55	μΑ
	1004	HALT modeNote 4		$V_{DD} = 3.0 \text{ V} \pm 10 \%$		5	15	μΑ
		VT4 V		$V_{DD} = 2.2 \text{ V} \pm 10 \%$		2.5	12.5	μΑ
	I _{DD5}	XT1 = V _{DD} STOP mode		$V_{DD} = 5.0 \text{ V} \pm 10 \%$		1	30	μΑ
	1555	When feedback resistor is conne	ected	$V_{DD} = 3.0 \text{ V} \pm 10 \%$		0.5	10	μΑ
				V _{DD} = 2.2 V ± 10 %		0.3	10	μΑ
	lass	XT1 = VDD		$V_{DD} = 5.0 \text{ V} \pm 10 \%$ $V_{DD} = 3.0 \text{ V} \pm 10 \%$		0.1	30	μΑ
	IDD6	When feedback resistor is disconr	STOP mode When feedback resistor is disconnected.			0.05	10	μΑ
		TTTOTT TO COLD CONTROL TO CO	Joica	$V_{DD} = 2.2 \text{ V} \pm 10 \%$		0.05	10	μΑ

Notes 1. Current flowing VdD and AVdD pin. Not including A/D converter, on-chip pull-up resistors or LCD dividing resistors.

- 2. Main system clock fxx = fx/2 operation (when oscillation mode selection register (OSMS) is set to 00H)
- **3.** Main system clock fxx = fx operation (when OSMS is set to 01H)
- **4.** When the main system clock is stopped.
- **5.** High-speed mode operation (when processor clock control register (PCC) is set to 00H)
- **6.** Low-speed mode operation (when PCC is set to 04H)

Remark Unless specified otherwise, the characteristics of dual-function pins are the same as the those of port pins.



DC CHARACTERISTICS (T_A = -10 to +85 °C)

(1) Static Display Mode (V_{DD} = 2.0 to 6.0 V)

Parameter	Symbol	Test Cond	MIN.	TYP.	MAX.	Unit	
LCD drive voltage	VLCD			2.0		V _{DD}	V
LCD dividing resistor	RLCD			60	100	150	kΩ
LCD output voltage deviation ^{Note} (common)	Vodc	Io = ±5 μA	2.0 V ≤ VLCD ≤ VDD	0		±0.2	V
LCD output voltage deviation ^{Note} (segment)	Vods	Io = ±1 μA	VLCD0 = VLCD	0		±0.2	V

Note The voltage deviation is the difference from the out voltage corresponding to the ideal value of the segment and common outputs (V_{LCDn} ; n = 0, 1, 2).

(2) 1/3 Bias Method ($V_{DD} = 2.5$ to 6.0 V)

Parameter	Symbol	Test Cond	MIN.	TYP.	MAX.	Unit	
LCD drive voltage	VLCD			2.5		V _{DD}	٧
LCD dividing resistor	RLCD			60	100	150	kΩ
LCD output voltage	Vodc	Io = ±5 μA	2.5 V ≤ VLCD ≤ VDD	0		±0.2	V
deviation ^{Note} (common)	. 050	ιο _ο μ. τ	VLCD0 = VLCD	,		_0	·
LCD output voltage	Vops	Io = ±1 μA	$V_{LCD1} = V_{LCD} \times \frac{2}{3}$	0		±0.2	V
deviationNote (segment)	V OD3	$0 = \pm 1 \mu$	$V_{LCD2} = V_{LCD} \times \frac{1}{3}$	0		±0.2	V

Note The voltage deviation is the difference from the out voltage corresponding to the ideal value of the segment and common outputs (V_{LCDn} ; n = 0, 1, 2).

(3) 1/2 Bias Method ($V_{DD} = 2.7$ to 6.0 V)

Parameter	Symbol	Test Cond	MIN.	TYP.	MAX.	Unit	
LCD drive voltage	VLCD			2.7		V _{DD}	V
LCD dividing resistor	RLCD			60	100	150	kΩ
LCD output voltage deviation ^{Note} (common)	Vodc	Io = ±5 μA	2.7 V ≤ VLCD ≤ VDD VLCD0 = VLCD	0		±0.2	V
LCD output voltage deviationNote(segment)	Vods	Io = ±1 μA	$V_{LCD1} = V_{LCD} \times \frac{1}{2}$ $V_{LCD2} = V_{LCD1}$	0		±0.2	V

Note The voltage deviation is the difference from the out voltage corresponding to the ideal value of the segment and common outputs (V_{LCDn} ; n = 0, 1, 2).



AC CHARACTERISTICS

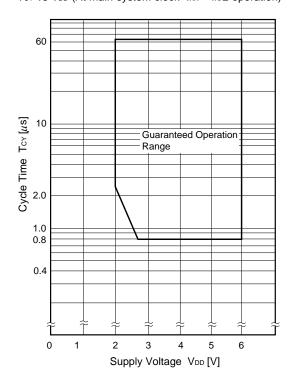
(1) Basic Operation (T_A = -40 to +85 °C, V_{DD} = 2.0 to 6.0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Cycle time (Min. instruction execution time)	Тсү	Operating on main system clock (fxx = 2.5 MHz) ^{Note 1}	V _{DD} = 2.7 to 6.0 V	0.8		64	μs
				2.2		64	μs
		Operating on main system clock	$4.5 \le V_{DD} \le 6.0 \text{ V}$	0.4		32	μs
		$(fxx = 5.0 \text{ MHz})^{\text{Note 2}}$	$2.7 \le V_{DD} < 4.5 V$	0.8		32	μs
		Operating on subsystem clock		40 ^{Note 3}	122	125	μs
TI00 input high/ low-level width	t тіноо,	4.5 V ≤ V _{DD} ≤ 6.0 V		2/f _{sam} +0.1 ^{Note 4}			μs
	t TILOO	2.7 V ≤ V _{DD} < 4.5 V		2/f _{sam} +0.2 ^{Note 4}			μs
		2.0 V ≤ V _{DD} < 2.7 V		2/f _{sam} +0.5 ^{Note 4}			μs
TI01 input high/ low-level width	t TIH01,	V _{DD} = 2.7 to 6.0 V		10			μs
	t TIL01			20			μs
TI input frequency	f⊤ı	V _{DD} = 4.5 to 6.0 V		0		4	MHz
				0		275	kHz
TI1, TI2 input high/low-level width	t тін,	V _{DD} = 4.5 to 6.0 V		100			ns
	t⊤ı∟			1.8			μs
Interrupt input	tinth,	INTP0		8/f _{sam} Note 4			μs
high/low-level	tintl	INTP1-INTP5, P110-P117	V _{DD} = 2.7 to 6.0 V	10			μs
width				20			μs
RESET low level width	t RST	V _{DD} = 2.7 to 6.0 V			10		μs
				20			μs

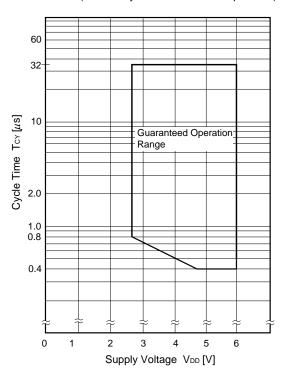
Notes 1. Main system clock fxx = fx/2 operation (when oscillation mode selection register (OSMS) is set to 00H)

- **2.** Main system clock fxx = fx operation (when OSMS is set to 01H)
- 3. This is the value when the external clock is used. The value is 114 μ s (min.) when the crystal resonator is used.
- **4.** In combination with bits 0 (SCS0) and 1 (SCS1) of sampling clock select register (SCS), selection of f_{sam} is possible between $f_{xx}/2^{N+1}$, $f_{xx}/32$, $f_{xx}/64$ and $f_{xx}/128$ (when N = 0 to 4).

Tcy vs V_{DD} (At main system clock fxx = fx/2 operation)



Tcy vs V_{DD} (At main system clock $f_{XX} = f_X$ operation)



- (2) Serial Interface (T_A = -40 to +85 °C, V_{DD} = 2.0 to 6.0 V)
 - (a) Serial interface channel 0

(i) 3-wire serial I/O mode (SCK0... Internal clock output)

. ,		*	• •			
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
		4.5 V ≤ V _{DD} ≤ 6.0 V	800			ns
SCK0 cycle time	tkcy1	2.7 V ≤ V _{DD} < 4.5 V	1600			ns
			3200			ns
SCK0 high/low-level width	t кн1,	V _{DD} = 4.5 to 6.0 V	tkcy1/2-50			ns
	t KL1		tксү1/2-100			ns
		$4.5 \text{ V} \leq \text{V}_{DD} \leq 6.0 \text{ V}$	100			ns
SI0 setup time (to SCK0↑)	t sıkı	2.7 V ≤ V _{DD} < 4.5 V	150			ns
			300			ns
SI0 hold time (from SCK0 1)	t ksıı		400			ns
SO0 output delay time from SCK0↓	t KSO1	C = 100 pF ^{Note}			300	ns

Note C is the load capacitance of SCKO, SOO output line.



(ii) 3-wire serial I/O mode (SCK0...External clock input)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
		4.5 V ≤ V _{DD} ≤ 6.0 V	800			ns
SCK0 cycle time	tkcy2	$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	1600			ns
			3200			ns
	t кн2,	$4.5 \text{ V} \leq \text{V}_{DD} \leq 6.0 \text{ V}$	400			ns
SCK0 high/low-level width	tKL2	$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	800			ns
	UNLZ		1600			ns
SI0 setup time (to SCK0↑)	tsık2		100			ns
SI0 hold time (from $\overline{SCK0}$ ↑)	tksı2		400			ns
SO0 output delay time from SCK0↓	t KSO2	C = 100 pF ^{Note}			300	ns
SCK0 rise, fall time	t _{R2} ,				1000	ns

Note C is the load capacitance of SO0 output line.

(iii) SBI mode (SCK0...Internal clock output)

Parameter	Symbol	Test	Conditions	MIN.	TYP.	MAX.	Unit
	,	V _{DD} = 4.5 to 6.0	V	800			ns
SCK0 cycle time	tксүз			3200			ns
SCK0 high/low-level	t кнз,	V _{DD} = 4.5 to 6.0	V	tксүз/2-50			ns
width	tкLз			tксүз/2-150			ns
SB0, SB1 setup time	tsik3	V _{DD} = 4.5 to 6.0	V	100			ns
(to SCK0↑)	tonto			300			ns
SB0, SB1 hold time (from SCK0↑)	t ksi3			tксүз/2			ns
SB0, SB1 output delay		$R = 1 k\Omega$,	V _{DD} = 4.5 to 6.0 V	0		250	ns
time from SCK0↓	t ks03	C = 100 pF ^{Note}		0		1000	ns
SB0, SB1↓from SCK0↑	t ksb		1	tксүз			ns
SCK0↓from SB0, SB1↓	tsвк			tксүз			ns
SB0, SB1 high-level width	tsвн			t ксүз			ns
SB0, SB1 low-level width	t sbl			tксүз			ns

Note R and C are the load resistance and load capacitance of the SCKO, SBO and SB1 output line.



(iv) SBI mode (SCK0...External clock input)

Parameter	Symbol	Test	Conditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy4	$V_{DD} = 4.5 \text{ to } 6.0$	V	800			ns
SCRO cycle time	IKCY4			3200			ns
SCK0 high/low-level	t кн4,	V _{DD} = 4.5 to 6.0	V	400			ns
width	tĸL4			1600			ns
SB0, SB1 setup time	tsik4	V _{DD} = 4.5 to 6.0	V	100			ns
(to SCK0↑)				300			ns
SB0, SB1 hold time (from $\overline{SCK0}$)	tksi4			tксү4/2			ns
SB0, SB1 output delay	tkso4	$R = 1 k\Omega$,	V _{DD} = 4.5 to 6.0 V	0		300	ns
time from SCK0↓		C = 100 pF ^{Note}		0		1000	ns
SB0, SB1↓from SCK0↑	tкsв		ı	tkcy4			ns
SCK0↓from SB0, SB1↓	tsвк			tkcy4			ns
SB0, SB1 high-level width	tsвн			tĸcy4			ns
SB0, SB1 low-level width	tsbl			tĸcy4			ns
SCK0 rise, fall time	t _{R4} ,					1000	ns

Note R and C are the load resistance and load capacitance of the SB0 and SB1 output line.

(v) 2-wire serial I/O mode (SCK0... Internal clock output)

Parameter	Symbol	Tes	Test Conditions		TYP.	MAX.	Unit
SCK0 cycle time			V _{DD} = 2.7 to 6.0 V	1600			ns
	tkCY5			3200			ns
CCKO bigh lovel width]	$V_{DD} = 2.7 \text{ to } 6.0 \text{ V}$	tксү5/2-160			ns
SCK0 high-level width	t _{KH5}			tксү5/2-190			ns
	tĸl5	D 410	V _{DD} = 4.5 to 6.0 V	tkcy5/2-50			ns
SCK0 low-level width		$R = 1 \text{ k}\Omega,$ $C = 100 \text{ pF}^{\text{Note}}$		tксү5/2-100			ns
SB0, SB1 setup time	tsik5		$4.5 \text{ V} \leq \text{V}_{DD} \leq 6.0 \text{ V}$	300			ns
(to SCK0↑)			2.7 V ≤ V _{DD} < 4.5 V	350			ns
(15 5 5 1 1 5 1)				400			ns
SB0, $\underline{\text{SB1}}$ hold time (from $\underline{\text{SCK0}}\uparrow$)	tksi5			600			ns
SB0, SB1 output delay time from SCK0↓	tks05					300	ns

Note R and C are the load resistance and load capacitance of the SCKO, SBO and SB1 output line.



(vi) 2-wire serial I/O mode (SCK0... External clock input)

Parameter	Symbol	Tes	st Conditions	MIN.	TYP.	MAX.	Unit
		$V_{DD} = 2.7 \text{ to } 6.$	0 V	1600			ns
SCK0 cycle time	tkcy6			3200			ns
001/01:11	4	$V_{DD} = 2.7 \text{ to } 6.$	0 V	650			ns
SCK0 high-level width	t кн6			1300			ns
	4	$V_{DD} = 2.7 \text{ to } 6.$	0 V	800			ns
SCK0 low-level width	t _{KL6}			1600			ns
SB0, SB1 setup time (to SCK0↑)	tsık6			100			ns
SB0, <u>SB1</u> hold time (from SCK0↑)	tksi6			t ксу6/2			ns
SB0, SB1 output delay	tkso6	$R = 1 k\Omega$,	V _{DD} = 4.5 to 6.0 V	0		300	ns
time from SCK0↓	1.300	C = 100 pF ^{Note}		0		500	ns
SCK0 rise, fall time	tre, tre					1000	ns

Note R and C are the load resistance and load capacitance of the SB0 and SB1 output line.

(b) Serial interface channel 2

(i) 3-wire serial I/O mode (SCK2... Internal clock output)

		• • •				
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
		4.5 V ≤ V _{DD} ≤ 6.0 V	800			ns
SCK2 cycle time	tkcy7	2.7 V ≤ V _{DD} < 4.5 V	1600			ns
			3200			ns
SCK2 high/low-level width	t кн7,	V _{DD} = 4.5 to 6.0 V	tксүт/2-50			ns
SCR2 High/low-level width	t _{KL7}		tксү7/2-100			ns
		4.5 V ≤ V _{DD} ≤ 6.0 V	100			ns
SI2 setup time (to SCK2↑)	t sık7	2.7 V ≤ V _{DD} < 4.5 V	150			ns
			300			ns
SI2 hold time (from SCK21)	t KSI7		400			ns
SO2 output delay time from SCK2↓	t ks01	C = 100 pF ^{Note}			300	ns

Note C is the load capacitance of $\overline{SCK2}$, SO2 output line.



(ii) 3-wire serial I/O mode (SCK2...External clock input)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
		4.5 V ≤ V _{DD} ≤ 6.0 V	800			ns
SCK2 cycle time	tkcy8	2.7 V ≤ V _{DD} < 4.5 V	1600			ns
			3200			ns
	t кн8,	$4.5 \text{ V} \leq \text{V}_{DD} \leq 6.0 \text{ V}$	400			ns
SCK2 high/low-level width		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	800			ns
	treo		1600			ns
SI2 setup time (to SCK2↑)	tsik8		100			ns
SI2 hold time (from SCK2↑)	tksi8		400			ns
SO2 output delay time from SCK2↓	tkso8	C = 100 pF ^{Note}			300	ns
SCK2 rise, fall time	t _{R8} ,				1000	ns

Note C is the load capacitance of SO2 output line.

(iii) UART mode (Dedicated baud rate generator output)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		4.5 V ≤ V _{DD} ≤ 6.0 V			78125	bps
		2.7 V ≤ V _{DD} < 4.5 V			39063	bps
					19531	bps

(iv) UART mode (External clock input)

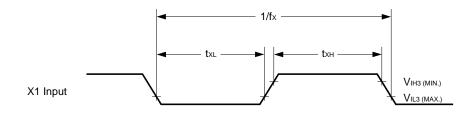
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
		4.5 V ≤ V _{DD} ≤ 6.0 V	800			ns
ASCK cycle time	t KCY9	2.7 V ≤ V _{DD} < 4.5 V	1600			ns
			3200			ns
1001/11/1/1	tuuo	4.5 V ≤ V _{DD} ≤ 6.0 V	400			ns
ASCK high/low-level width	tkH9,	2.7 V ≤ V _{DD} < 4.5 V	800			ns
Width	ikl9		1600			ns
		4.5 V ≤ V _{DD} ≤ 6.0 V			39063	bps
Transfer rate		2.7 V ≤ V _{DD} < 4.5 V			19531	bps
					9766	bps
ASCK rise, fall time	tre, tre				1000	ns

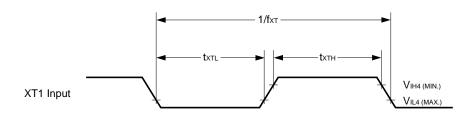


AC Timing Test Point (Excluding X1, XT1 Input)

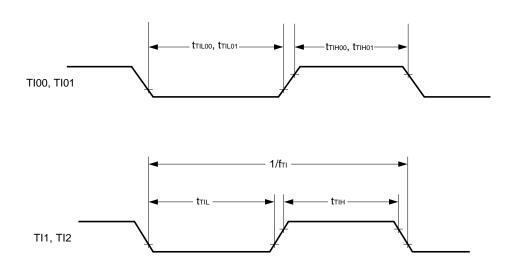


Clock Timing





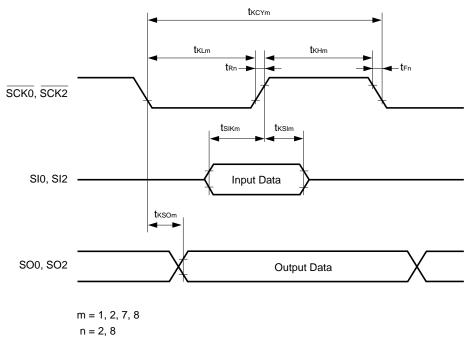
TI Timing



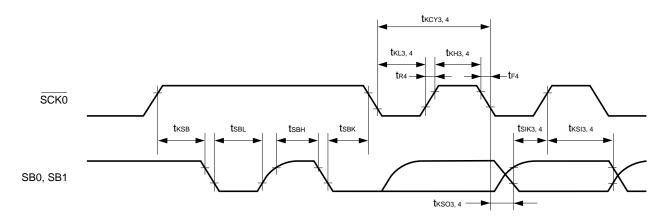


Serial Transfer Timing

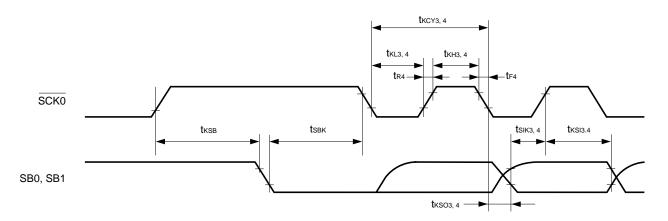
3-wire serial I/O mode:



SBI mode (bus release signal transfer):

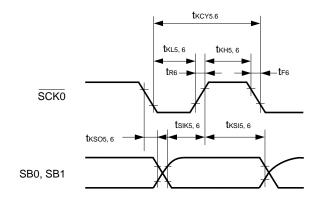


SBI mode (command signal transfer):

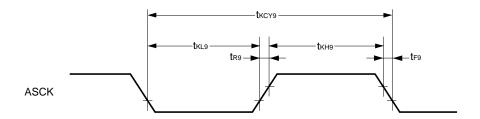




2-wire serial I/O mode:



UART mode:



A/D Converter (TA = -40 to +85 $^{\circ}$ C, AVDD = VDD = 4.5 to 6.0 V, AVss = Vss = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bit
Overall error Note		4.5 V ≤ AV _{REF} ≤ AV _{DD}			2.0	%
Conversion time	tconv		19.1		200	μs
Sampling time	t samp		12/fxx			μs
Analog input voltage	VIAN		AVss		AVREF	V
Reference voltage	AVREF		2.0		AV _{DD}	V
AVREF-AVss resistance	RAIREF		4	14		kΩ

Note Quantization error $(\pm 1/2 \text{ LSB})$ is not included. This is expressed in proportion to the full-scale value.

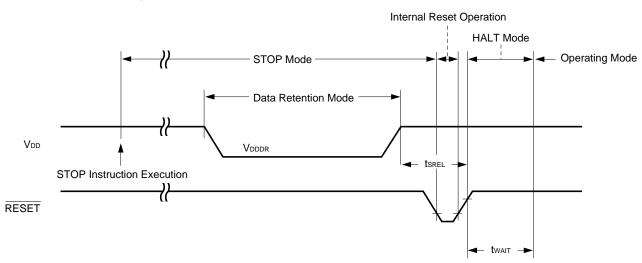


DATA MEMORY STOP MODE LOW SUPPLY VOLTAGE DATA RETENTION CHARACTERISTICS ($T_A = -40$ to +85 °C)

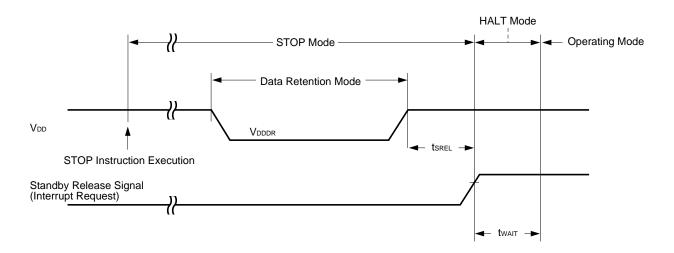
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.8		6.0	V
Data retention power supply current	Idddr	VDDDR = 1.8 V Subsystem clock stop and feed-back resistor disconnected		0.1	10	μΑ
Release signal set time	tsrel		0			μs
Oscillation		Release by RESET		217/fx		ms
stabilization wait time	t wait	Release by interrupt		Note		ms

Note In combination with bits 0 to 2 (OSTS0 to OSTS2) of oscillation stabilization time select register (OSTS), selection of 2¹²/fxx and 2¹⁴/fxx to 2¹⁷/fxx is possible.

Data Retention Timing (STOP Mode Release by RESET)

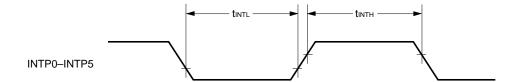


Data Retention Timing (Standby Release Signal: STOP Mode Release by Interrupt Signal)

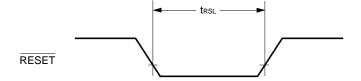




Interrupt Input Timing



RESET Input Timing





PROM PROGRAMMING CHARACTERISTICS

DC Characteristics

(1) PROM Write Mode (Ta = 25 \pm 5 °C, VdD = 6.5 \pm 0.25 V, VpP = 12.5 \pm 0.3 V)

Parameter	Symbol	Symbol ^{Note}	Test Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	ViH	Vıн		0.7 Vdd		V _{DD}	V
Input voltage, low	VıL	VıL		0		0.3 VDD	V
Output voltage, high	Vон	Vон	Iон = −1 mA	V _{DD} -1.0			V
Output voltage, low	Vol	Vol	IoL = 1.6 mA			0.4	V
Input leakage current	lu	lu	$0 \le V_{IN} \le V_{DD}$	-10		+10	μΑ
VPP supply voltage	V _{PP}	V _{PP}		12.2	12.5	12.8	V
V _{DD} supply voltage	V _{DD}	Vcc		6.25	6.5	6.75	V
VPP supply current	IPP	IPP	PGM = VIL			50	mA
V _{DD} supply current	IDD	Icc				50	mA

Note Symbol corresponding to the μ PD27C1001A.

(2) PROM Read Mode (TA = 25 \pm 5 °C, VDD = 5.0 \pm 0.5 V, VPP = VDD \pm 0.6 V)

Parameter	Symbol	Symbol ^{Note}	Test Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	ViH	ViH		0.7 V _{DD}		V _{DD}	V
Input voltage, low	VIL	VıL		0		0.3 V _{DD}	V
Output voltage high	V _{OH1}	Vон1	Iон = −1 mA	V _{DD} -1.0			V
Output voltage, high	V _{OH2}	V _{OH2}	Ioн = −100 μA	V _{DD} -0.5			V
Output voltage, low	Vol	Vol	IoL = 1.6 mA			0.4	V
Input leakage current	Iμ	lu	$0 \le V_{IN} \le V_{DD}$	-10		+10	μΑ
Output leakage current	ILO	lıo	$0 \le V_{OUT} \le V_{DD}, \overline{OE} = V_{IH}$	-10		+10	μΑ
VPP supply voltage	V _{PP}	V _{PP}		V _{DD} -0.6	V _{DD}	V _{DD} +0.6	V
V _{DD} supply voltage	V _{DD}	Vcc		4.5	5.0	5.5	V
VPP supply current	IPP	I PP	VPP = VDD			100	μΑ
V _{DD} supply current	IDD	ICCA1	CE = VIL, VIN = VIH			50	mA

Note Symbol corresponding to the μ PD27C1001A.



AC Characteristics

(1) PROM Write Mode

(a) Page program mode (TA = 25 \pm 5 °C, VDD = 6.5 \pm 0.25 V, VPP = 12.5 \pm 0.3 V)

Parameter	Symbol	Symbol ^{Note}	Test Conditions	MIN.	TYP.	MAX.	Unit
Address setup time (to $\overline{OE} \downarrow$)	tas	tas		2			μs
OE setup time	toes	toes		2			μs
CE setup time (to OE↓)	tces	tces		2			μs
Input data setup time (to OE↓)	tos	tos		2			μs
	tан	t AH		2			μs
Address hold time (from OE ↑)	t ahl	t ahl		2			μs
	t ahv	t ahv		0			μs
Input data hold time (from OE↑)	tон	t DH		2			μs
Data output float delay time from OE↑	tof	t DF		0		250	ns
V _{PP} setup time (to $\overline{\text{OE}}$ ↓)	tvps	tvps		1.0			ms
V_{DD} setup time (to $\overline{OE} \downarrow$)	tvds	tvcs		1.0			ms
Program pulse width	tpw	tpw		0.095	0.1	0.105	ms
Valid data delay time from OE ↓	toe	toe				1	μs
OE pulse width during data latching	tLW	t LW		1			μs
PGM setup time	t PGMS	t PGMS		2			μs
CE hold time	t ceн	tсен		2			μs
OE hold time	tоен	tоен		2			μs

Note Corresponding μ PD27C1001A symbol

(b) Byte program mode (TA = 25 \pm 5 °C, VDD = 6.5 \pm 0.25 V, VPP = 12.5 \pm 0.3 V)

Parameter	Symbol	Symbol ^{Note}	Test Conditions	MIN.	TYP.	MAX.	Unit
Address setup time (to $\overline{\text{PGM}} \downarrow$)	t as	tas		2			μs
OE setup time	toes	toes		2			μs
CE setup time (to PGM↓)	tces	tces		2			μs
Input data setup time (to PGM ↓)	tos	tos		2			μs
Address hold time (from OE↑)	tан	t AH		2			μs
nput data hold time (from PGM↑)	tон	tон		2			μs
Data output float delay time from OE↑	t DF	t DF		0		250	ns
V _{PP} setup time (to $\overline{\text{PGM}}$ ↓)	tvps	tvps		1.0			ms
V _{DD} setup time (to \overline{PGM} ↓)	tvos	tvcs		1.0			ms
Program pulse width	t pw	t PW		0.095	0.1	0.105	ms
Valid data delay time from OE↓	toe	toe				1	μs
OE hold time	tоен			2			μs

Note Corresponding μ PD27C1001A symbol



(2) PROM Read Mode (TA = 25 \pm 5 °C, VDD = 5.0 \pm 0.5 V, VPP = VDD \pm 0.6 V)

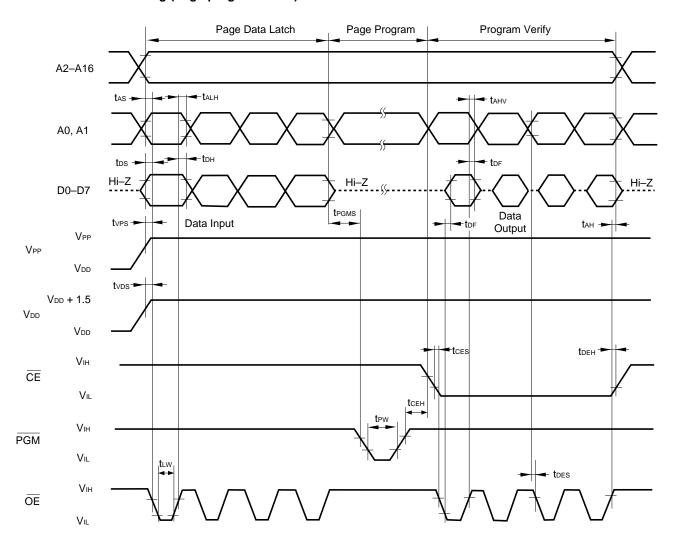
Parameter	Symbol	Symbol ^{Note}	Test Conditions	MIN.	TYP.	MAX.	Unit
Data output time from address	tacc	tacc	$\overline{CE} = \overline{OE} = V_{IL}$			800	ns
Data output delay time from $\overline{CE} \downarrow$	tce	t CE	OE = VIL			800	ns
Data output delay time from $\overline{OE} \downarrow$	toe	toe	CE = VIL			200	ns
Data output float delay time from OE↑	t DF	t DF	CE = VIL	0		60	ns
Data hold time from address	tон	tон	CE = OE = VIL	0			ns

Note Corresponding μ PD27C1001A symbol

(3) PROM Programming Mode Setting ($T_A = 25$ °C, $V_{SS} = 0$ V)

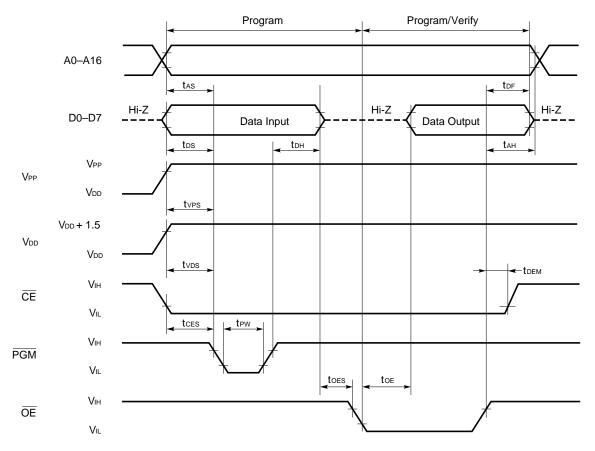
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
PROM programming mode setup time	tsма		10			μs

PROM Write Mode Timing (Page program mode)



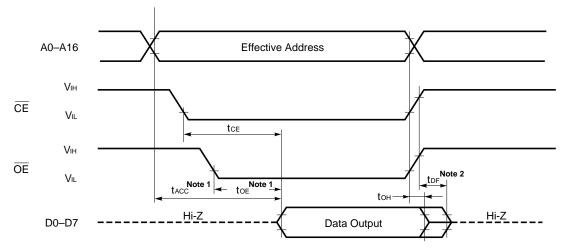


PROM Write Mode Timing (Byte program mode)



- Cautions 1. VDD must be applied before VPP and cut off after VPP.
 - 2. VPP must not exceed +13.5 V including overshoot.
 - 3. Removing and reinserting may adversely affect in reliability while +12.5 V is applied to VPP.

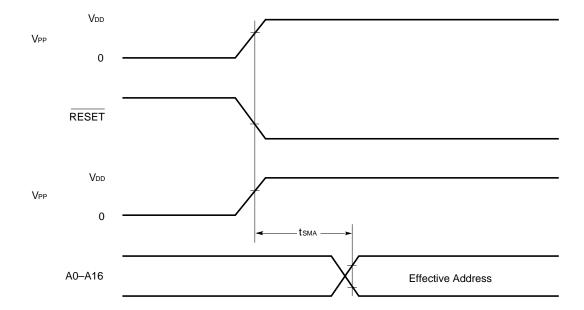
PROM Read Mode Timing



- Notes 1. When reading within the tacc range, the \overline{OE} input delay time from the \overline{CE} fall time must be maximum of tacc toe.
 - 2. toF is the time from the point at which either \overline{OE} or \overline{CE} (whichever is first) reaches V_{IH}.



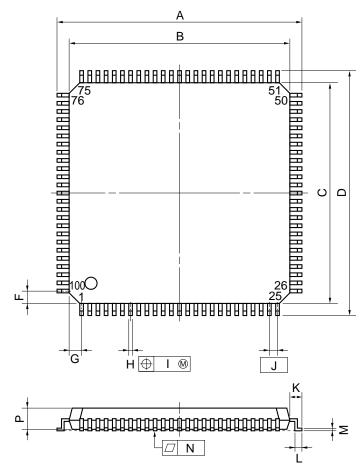
PROM Programming Mode Setting Timing



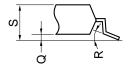


7. PACKAGE DRAWINGS

100 PIN PLASTIC QFP (FINE PITCH) (□14)



detail of lead end



NOTE

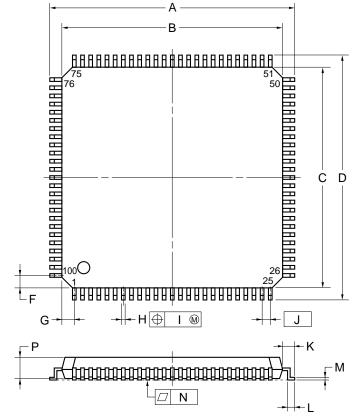
Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

Remark	Dimensions and materials of ES products are the
	same as those of the mass production product.

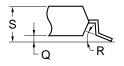
ITEM	MILLIMETERS	INCHES
Α	16.0±0.2	0.630±0.008
В	14.0±0.2	$0.551^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	16.0±0.2	0.630±0.008
F	1.0	0.039
G	1.0	0.039
Н	$0.22^{+0.05}_{-0.04}$	0.009±0.002
1	0.10	0.004
J	0.5 (T.P.)	0.020 (T.P.)
K	1.0±0.2	$0.039^{+0.009}_{-0.008}$
L	0.5±0.2	0.020+0.008
М	0.17 + 0.03 - 0.07	0.007+0.001
N	0.10	0.004
Р	1.45	0.057
Q	0.125±0.075	0.005±0.003
R	5°±5°	5°±5°
S	1.7 MAX.	0.067 MAX.
		2100GC-50-7EA-2

P100GC-50-7EA-2

100 PIN PLASTIC LQFP (FINE PITCH) (14×14)



detail of lead end



NOTE

Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.

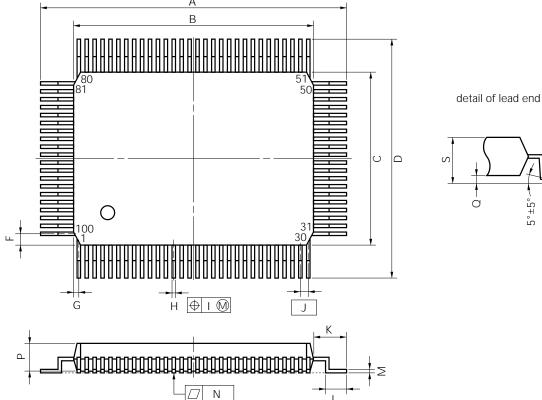
ITEM	MILLIMETERS	INCHES
Α	16.00±0.20	0.630±0.008
В	14.00±0.20	0.551 ^{+0.009} -0.008
С	14.00±0.20	$0.551^{+0.009}_{-0.008}$
D	16.00±0.20	0.630±0.008
F	1.00	0.039
G	1.00	0.039
Н	$0.22^{+0.05}_{-0.04}$	0.009±0.002
I	0.08	0.003
J	0.50 (T.P.)	0.020 (T.P.)
K	1.00±0.20	$0.039^{+0.009}_{-0.008}$
L	0.50±0.20	0.020+0.008
М	0.17+0.03	0.007+0.001
N	0.08	0.003
Р	1.40±0.05	0.055±0.002
Q	0.10±0.05	0.004±0.002
R	3°+7° -3°	3°+7° -3°
S	1.60 MAX.	0.063 MAX.
	· · · · · · · · · · · · · · · · · · ·	CAOOCC EO OFII

S100GC-50-8EU

Remark Dimensions and materials of ES products are the same as those of the mass production product.



100 PIN PLASTIC QFP (14 × 20)



NOTE

Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

		P100GF-65-3BA1-2
ITEM	MILLIMETERS	INCHES
А	23.6±0.4	0.929±0.016
В	20.0±0.2	0.795+0.009
С	14.0±0.2	0.551+0.009
D	17.6±0.4	0.693±0.016
F	0.8	0.031
G	0.6	0.024
Н	0.30±0.10	0.012+0.004
I	0.15	0.006
J	0.65 (T.P.)	0.026 (T.P.)
K	1.8±0.2	0.071+0.008
L	0.8±0.2	0.031+0.009
М	0.15 ^{+0.10} _{-0.05}	0.006+0.004
N	0.10	0.004
Р	2.7	0.106
Q	0.1±0.1	0.004±0.004
S	3.0 MAX.	0.119 MAX.

Remark

Dimensions and materials of ES products are the same as those of the mass production product.



8. RECOMMENDED SOLDERING CONDITIONS

The μ PD78P064B should be soldered and mounted under the conditions recommended in the table below. For detail of recommended soldering conditions, refer to the information document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact our sales personnel.

Table 8-1. Surface Mounting Type Soldering Conditions

(1) μ PD78P064BGC-7EA: 100-pin plastic QFP (fine pitch) (14 × 14 mm) μ PD78P064BGC-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14 mm)

Soldering Method	Soldering Conditions	Recommended Soldering Symbols
Infrared reflow	Package peak temperature: 235 °C, Duration: 30 sec. max. (at 210 °C or above), Number of times: Twice max., Time limit: 7 days ^{Note} (thereafter 10 hours prebaking required at 125 °C) <precaution> Products cannot be baked while packed in anything other than in a heat resistant tray (i.e. they cannot be baked in a magazine, taping, or heat-labile tray).</precaution>	IR35-107-2
VPS	Package peak temperature: 235 °C, Duration: 30 sec. max. (at 210 °C or above), Number of times: Twice max., Time limit: 7 days ^{Note} (thereafter 10 hours prebaking required at 125 °C) <precaution> Products cannot be baked while packed in anything other than in a heat resistant tray (i.e. they cannot be baked in a magazine, taping, or heat-labile tray).</precaution>	VP15-107-2
Partial heating	Pin temperature: 300 °C max., Duration: 3 sec. max. (per device side)	

Note For the storage period after dry-pack decapsulation, storage conditions are max. 25 °C, 65 % RH.

(2) μ PD78P064BGF-3BA: 100-pin plastic QFP (14 × 20 mm)

Soldering Method	Soldering Conditions	Recommended Soldering Symbols
Infrared reflow	Package peak temperature: 235 °C, Duration: 30 sec. max. (at 210 °C or above), Number of times: Three times max.	IR35-00-3
VPS	Package peak temperature: 215 °C, Duration: 40 sec. (at 200 °C or above), Number of times: Three times max.	VP15-00-3
Wave soldering	Solder bath temperature: 260 °C max., Duration: 10 sec. max., Number of times: Once, Preheating temperature: 120 °C max. (Package surface temperature)	WS60-00-1
Partial heating	Pin temperature: 300 °C max., Duration: 3 sec. max. (per device side)	_

Caution Use of more than one soldering method should be avoided (except in the case of partial heating).



APPENDIX A. DEVELOPMENT TOOLS

The following development tools are available for system development using $\mu PD78P064B$.

Language Processing Software

RA78K/0Note 1, 2, 3, 4	78K/0 series common assembler package	
CC78K/0Note 1, 2, 3, 4	78K/0 series common C compiler package	
DF78064 ^{Note 1, 2, 3, 4}	μ PD78064 subseries common device file	
CC78K/0-LNote 1, 2, 3, 4	78K/0 series common C compiler library source file	

PROM Writing Tools

PG-1500	PROM programmer
PA-78P064GC	Programmer adapters connected to PG-1500
PA-78P064GF	
PA-PG-1500 controllerNote 1, 2	PG-1500 control program

Debugging Tools

IE-78000-R	78K/0 series common in-circuit emulators
IE-78000-R-A	78K/0 series common in-circuit emulators (for integrated debugger)
IE-78000-R-BK	78K/0 series common break board
IE-780308-R-EM	μPD780308 subseries common evaluation emulation boards
EP-78064GC-R	μ PD78064 subseries common emulation probes
EP-78064GF-R	
TGC-100SDW	Adapter to be mounted on a target system board made for 100-pin plastic QFP (GC-7EA, GC-8EU type) A product of Tokyo Eletech Corp. (Tokyo 03-5295-1661). When purchasing this product, consult your NEC distributor.
EV-9200GF-100	Socket to be mounted on a target system board made for 100-pin plastic QFP (GF-3BA type)
SM78K0 ^{Note 5, 6, 7}	78K/0 series common system simulators
ID78K0 ^{Note 4, 5, 6, 7}	IE-78000-R-A integrated debuggers
SD78K/0 ^{Note 1, 2}	IE-78000-R screen debuggers
DF78064Note 1, 2, 4, 5, 6, 7	μ PD78064 subseries common device file

Real-Time OS

RX78K/0 ^{Note 1, 2, 3, 4}	78K/0 series real-time OS
MX78K/0 ^{Note 1, 2, 3, 4}	78K/0 series OS

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Fuzzy Inference Development Support System

FE9000 ^{Note 1} , FE9200 ^{Note 6}	Fuzzy knowledge data creation tool
FT9080 ^{Note 1} , FT9085 ^{Note 2}	Translator
FI78K/ Note 1, 2	Fuzzy inference module
FD78K/IINote 1, 2	Fussy inference debugger

Notes 1. PC-9800 series (MS-DOS™) based

- 2. IBM PC/AT™ and compatible machines (PC DOS™/IBM DOS™/MS-DOS) based
- 3. HP9000 series 300^{TM} (HP-UXTM) based
- **4.** HP9000 series 700[™] (HP-UX) based, SPARCstation[™] (SunOS[™]) based, EWS4800 series (EWS-UX/V) based
- **5.** PC-9800 series (MS-DOS + Windows™) based
- 6. IBM PC/AT and compatible machines (PC DOS/IBM DOS/MS-DOS + Windows) based
- 7. NEWS™ (NEWS-OS™) based

- Remarks 1. For third party development tools, refer to 78K/0 Series Selection Guide (U11126E).
 - 2. RA78K/0, CC78K/0, SM78K0, ID78K0, SD78K/0, and RX78K/0 are used in combination with DF78064.



CONVERSION SOCKET (EV-9200GF-100) PACKAGE DRAWINGS AND RECOMMENDED BOARD MOUNTING PATTERN

No.1 pin index

Figure A-1. EV-9200GF-100 Package Drawing

ITEM	MILLIMETERS INCHES	
А	24.6	0.969
В	21	0.827
С	15	0.591
D	18.6	0.732
Е	4-C 2	4-C 0.079
F	0.8	0.031
G	12.0	0.472
Н	22.6	0.89
I	25.3	0.996
J	6.0	0.236
K	16.6	0.654
L	19.3	076
М	8.2	0.323
Ν	8.0	0.315
0	2.5	0.098
Р	2.0	0.079
Q	0.35	0.014
R	φ2.3	ø0.091
S	ø 1.5	Ø0.059

Κ ш С В Α

Figure A-2. EV-9200GF-100 Board Mounting Pattern

EV-9200GF-100-P0

ITEM	MILLIMETERS	INCHES
А	26.3	1.035
В	21.6	0.85
С	$0.65\pm0.02\times29=18.85\pm0.05$	$0.026^{+0.001}_{-0.002} \times 1.142 = 0.742^{+0.002}_{-0.002}$
D	$0.65\pm0.02\times19=12.35\pm0.05$	$0.026^{+0.001}_{-0.002} \times 0.748 = 0.486^{+0.003}_{-0.002}$
Е	15.6	0.614
F	20.3	0.799
G	12±0.05	$0.472^{+0.003}_{-0.002}$
Н	6±0.05	$0.236^{+0.003}_{-0.002}$
I	0.35±0.02	$0.014^{+0.001}_{-0.001}$
J	\$\phi_2.36±0.03\$	ϕ 0.093 $^{+0.001}_{-0.002}$
K	\$ 2.3	Ø0.091
L	φ1.57±0.03	\$\phi_{0.062^{+0.001}_{-0.002}}\$

Caution Dimensions of mount pad for EV-9200 and that for target

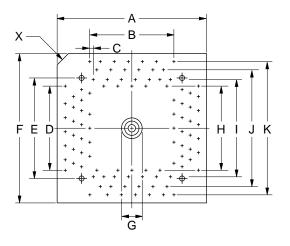
device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).

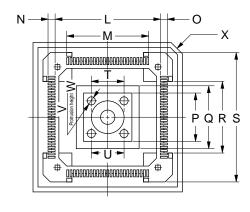


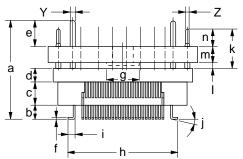
★ CONVERSION ADAPTER (TGC-100SDW) PACKAGE DRAWINGS

Figure A-3. TGC-100SDW Package Drawing

Reference diagram: TGC-100SDW Package dimension (unit: mm)







ITEM MILLIMETERS		INCHES		
Α	21.55	0.848		
В	0.5x24=12	0.020x0.945=0.472		
С	0.5	0.020		
D	0.5x24=12	0.020x0.945=0.472		
E	15.0	0.591		
F	21.55	0.848		
G	ϕ 3.55	φ0.140		
Н	10.9	0.429		
T	13.3	0.524		
J	15.7	0.618		
K	18.1	0.713		
L	13.75	0.541		
М	0.5x24=12.0	0.020x0.945=0.472		
N	1.125±0.3	0.044±0.012		
0	1.125±0.2	0.044±0.008		
Р	7.5	0.295		
Q	10.0	0.394		
R	11.3	0.445		
S	18.1	0.713		
Т	φ5.0	φ0.197		
U	5.0	0.197		
V	4- <i>\phi</i> 1.3	4-φ0.051		
W	1.8	0.071		
X	C 2.0	C 0.079		
Y	φ0.9	φ0.035		
Z	φ0.3	φ0.012		

ITEM	MILLIMETERS	INCHES
a	14.45	0.569
b	1.85±0.25	0.073±0.010
С	3.5	0.138
d	2.0	0.079
е	3.9	0.154
f	0.25	0.010
g	ϕ 4.5	ϕ 0.177
h	16.0	0.630
i	1.125±0.3	0.044±0.012
j	0~5°	0.000~0.197°
k	5.9	0.232
- 1	0.8	0.031
m	2.4	0.094
n	2.7	0.106
		TGC-100SDW-G0E

TGC-100SDW-G0E

Remark Manufactured by Tokyo Eletech Corp.



APPENDIX B. RELATED DOCUMENTS

Device Related Documents

Document Name	Document No.	
Document Name	Japanese	English
μPD78064B Subseries User's Manual	U10785J	U10785E
μPD78064B Data Sheet	U11590J	U11590E
μPD78P064B Data Sheet	U11598J	This document
78K/0 Series User's Manual (Instruction)	U12326J	U12326E
78K/0 Series Instruction List	U10903J	_
78K/0 Series Instruction Set	U10904J	_
μPD78064B Subseries Special Function Register Table	Planned	_

Development Tool Related Documents (User's Manual) (1/2)

Document Name		Document No.	
		Japanese	English
RA78K Series Assembler Package	Operation	EEU-809	EEU-1399
	Language	EEU-815	EEU-1404
RA78K Series Structured Assembler Preproce	ssor	EEU-817	EEU-1402
RA78K0 Assembler Package	Operation	U11802J	U11802E
	Assembly language	U11801J	U11801E
	Structured assembly language	U11789J	U11789E
CC78K Series C Compiler	Operation	EEU-656	EEU-1280
	Language	EEU-655	EEU-1284
CC78K0 C Compiler	Operation	U11517J	U11517E
	Language	U11518J	U11518E
CC78K/0 C Compiler Application Note	Programming know-how	EEA-618	EEA-1208
CC78K Series Library Source File		U12322J	_
PG-1500 PROM Programmer		U11940J	U11940E
PG-1500 Controller PC-9800 Series (MS-DOS) Based	EEU-704	EEU-1291
PG-1500 Controller IBM PC Series (PC DOS)	Based	EEU-5008	U10540E
IE-78000-R		U11376J	U11376E
IE-78000-R-A		U10057J	U10057E
IE-78000-R-BK		EEU-867	EEU-1427
IE-780308-R-EM		U11362J	U11362E
EP-78064		EEU-934	EEU-1469



Development Tool Related Documents (User's Manual) (2/2)

Document Name		Document No.	
		Japanese	English
SM78K0 System Sumilator Windows Based	Reference	EEU-5002	U10181E
SM78K Series System Simulator	External components user open interface specification	U10092J	U10092E
ID78K0 Integrated Debugger EWS Based	Reference	U11151J	_
ID78K0 Integrated Debugger PC Based	Reference	U11539J	U11539E
ID78K0 Integrated Debugger Windows Based	Guide	U11649J	U11649E
SD78K/0 Screen Debugger	Introduction	EEU-852	U10539E
PC-9800 Series (MS-DOS) Based	Reference	U10952J	_
SD78K/0 Screen Debugger	Introduction	EEU-5024	EEU-1414
IBM PC/AT (PC DOS) Based	Reference	U11279J	U11279E

Caution The above related documents are subject to change without notice. For design purpose, etc., be sure to use the latest documents.

Embedded Software Related Documents (User's Manual)

Document Name		Document No.	
		Japanese	English
78K/0 Series Real-Time OS	Basic	U11537J	_
	Installation	U11536J	_
78K/0 Series OS MX78K0	Basic	U12257J	_
Fuzzy Knowledge Data Creation Tool		EEU-829	EEU-1438
78K/0, 78K/II, 87AD Series Fuzzy Inference Development Support System Translator		EEU-862	EEU-1444
78K/0 Series Fuzzy Inference Development Support System Fuzzy Inference Module		EEU-858	EEU-1441
78K/0 Series Fuzzy Inference Development Support System Fuzzy Inference Debugger		EEU-921	EEU-1458

Other Related Documents

Document Name	Document No.	
Dodalielik Nalile	Japanese	English
IC Package Manual	C10943X	
Semiconductor Device Mounting Technology Manual	C10535J	C10535E
Quality Grades on Semiconductor Devices	C11531J	C11531E
NEC Semiconductor Device Reliability and Quality Control	C10983J	C10983E
Electrostatic Discharge (ESD) Test	MEM-539	_
Semiconductor Devices Quality Guarantee Guide	C11893J	MEI-1202
Microcomputer-Related Product Guide (Products by Other Manufacturers)	U11416J	_

Caution The above related documents are subject to change without notice. For design purpose, etc., be sure to use the latest documents.

NEC μ PD78P064B

[MEMO]

NOTES FOR CMOS DEVICES -

1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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- · Device availability
- · Ordering information
- · Product release schedule
- · Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- · Network requirements

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.